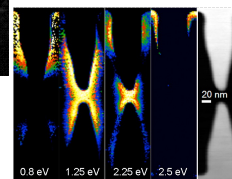
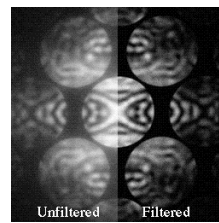
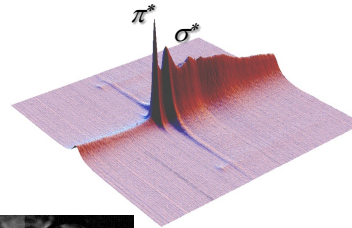


Electron Energy Loss Spectroscopy



1

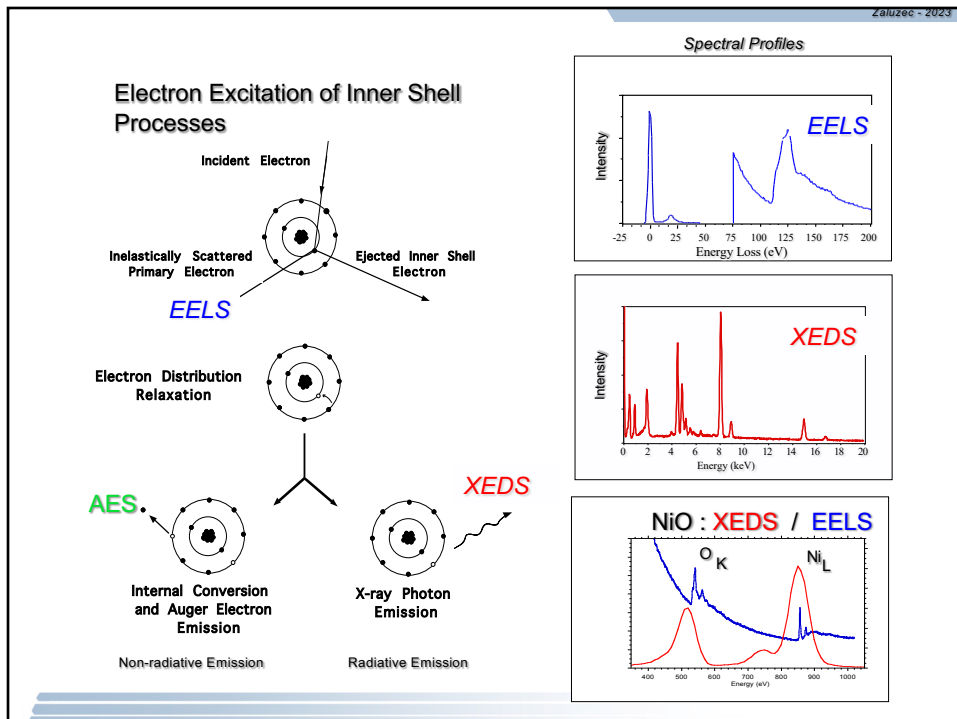
The Energy Loss Processes
Instrumentation: Detector Systems
Instrumentation: AEM Systems
Data Analysis and Quantification:
Advanced Topics

2

Electron Energy Loss Spectroscopy

- Measure the changes in the inelastic scattering distribution of an electron beam transmitted through a **thin** specimen.
- Each type of interaction between the electron beam and the specimen produces a **characteristic** change in the energy and angular distribution of scattered electrons.
- The energy loss process is the **primary** interaction event. All other sources of analytical information (i.e. X-rays, Auger electrons, etc.) are **secondary** products of the initial inelastic event. Thus, EELS has the highest potential yield of information/inelastic event

3

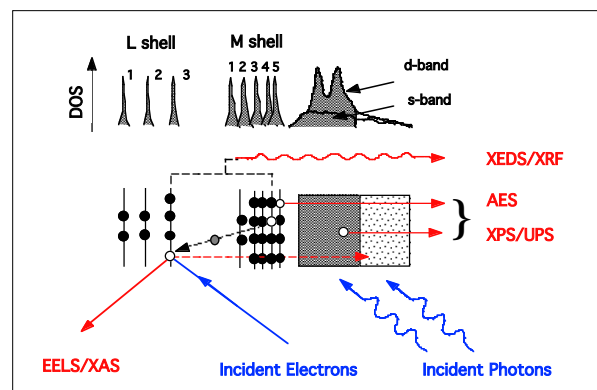


4

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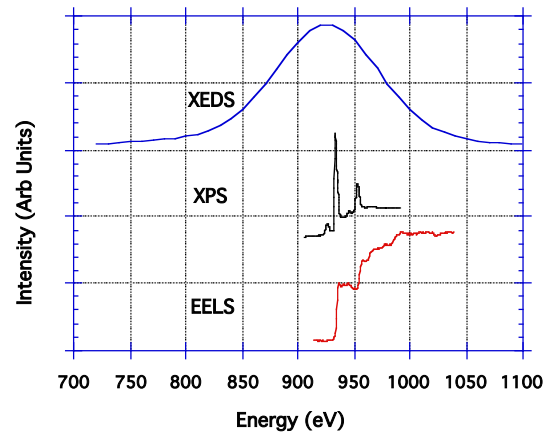
5



Schematic Diagram Illustrating Sources of Inelastic Scattering Signals

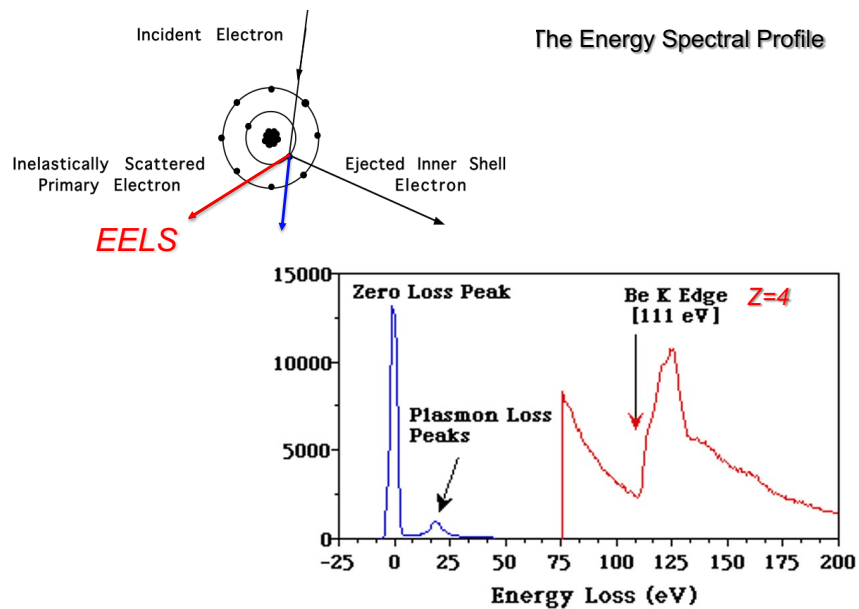
6

Experimental XEDS, XPS, and EELS data from the Copper L shell. Note the differences in energy resolution, and spectral features.



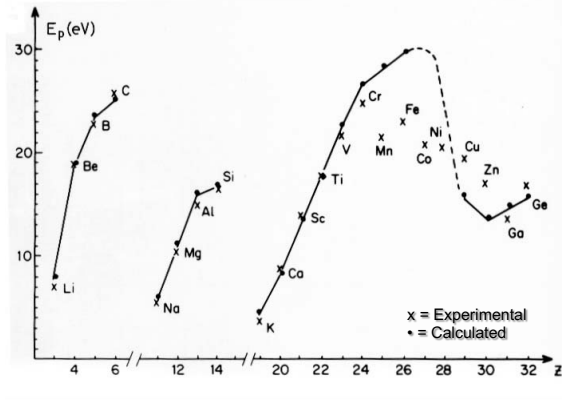
7

The Energy Spectral Profile



8

Plasmon Energies of some Elements



$$E_p = (h/2\pi)(ne^2/\epsilon_0 m)^{1/2} = (28.8\text{eV}) (z\rho/A)^{1/2}$$

n = density of "outer-shell" electrons,
 z = valency (free-e/atom)

Colliex 1984

9

Table 1. Edges Suitable for EELS Microanalysis
for the Energy Range 0-3 keV

Atomic Number	Inner Shell	Spectroscopic Notation
$Z = 1-11$	K	1s
$Z = 12-17$	K L ₃ , L ₂ , L ₁	1s 2p _{3/2} , 2p _{1/2} , 2s
$Z = 19-45$	L ₃ , L ₂ , L ₁ M ₅₄ , M ₃₂ , M ₁	2p _{3/2} , ... 3d _{5/2} , 3d _{3/2} , 3d _{1/2} , 3p _{3/2} , 3p _{1/2} , 3s
$Z = 46-79$	M ₅₄ , M ₃₂ , M ₁ N ₄₅ , N ₃₂ , N ₁ O ₃₂ , O ₁	3d _{5/2} , ... 4d _{5/2} , 4d _{3/2} , 4d _{1/2} , 4p _{3/2} , 4p _{1/2} , 4s 5p _{3/2} , 5p _{1/2} , 5s
$Z > 80$	N ₆₇ , N ₄₅ , N ₃₂ , N ₁ O ₄₅ , O ₃₂ , O ₁	4f _{7/2} , ... 5p _{3/2} , ...

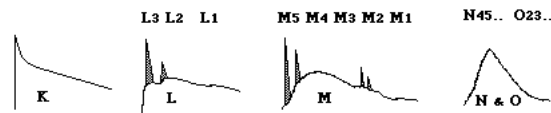
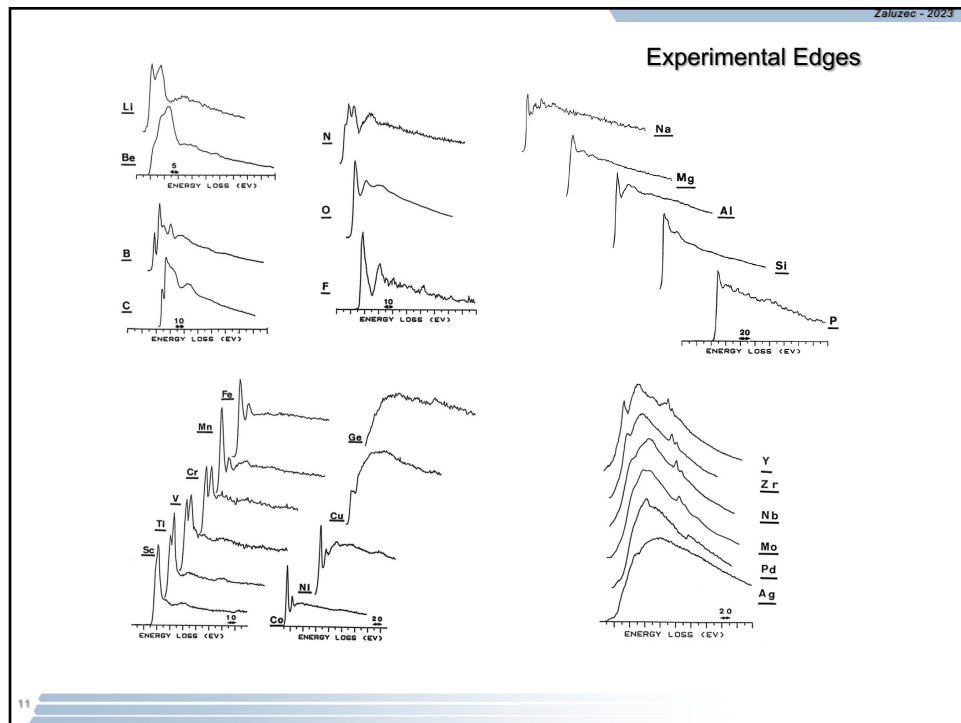


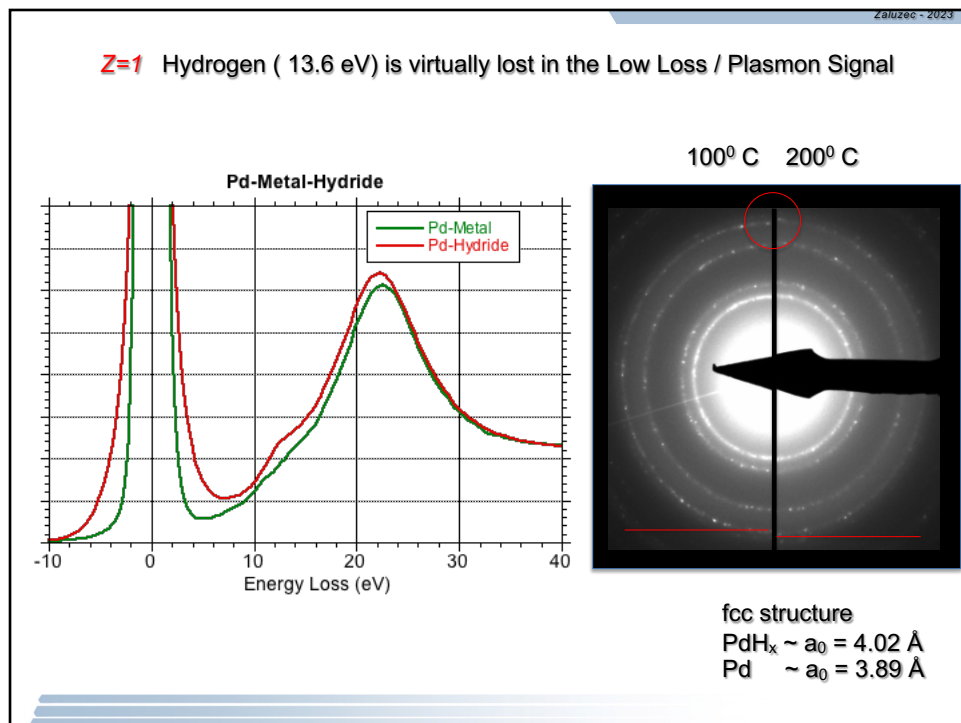
Figure 5. Schematic illustration of K, L, M, N and O Edge shapes, the "white lines" sometimes detected on L and M shells are shown shaded peaks at the edge onsets. In all sketches the background shape has been omitted for clarity. These profiles should be compared with experimental profiles of figure 6.

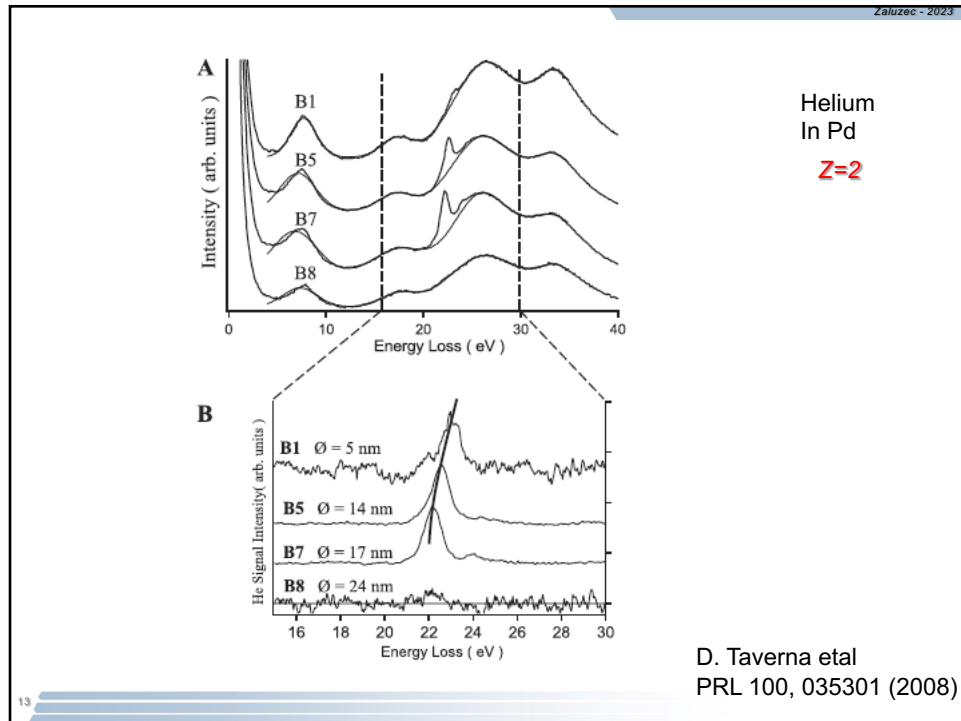
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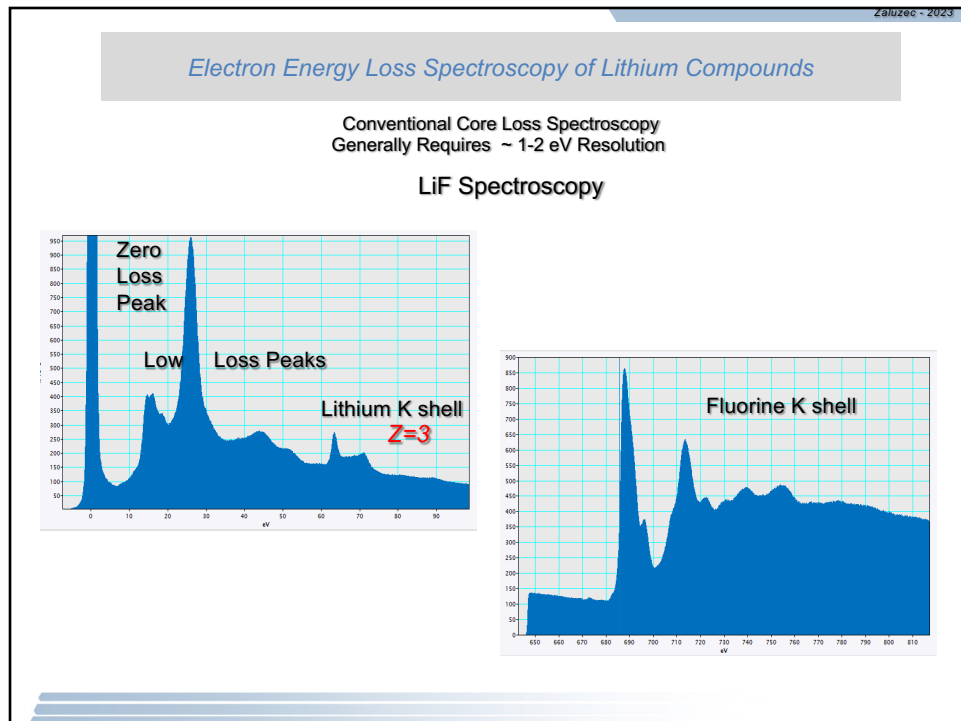


11





13



Electron Scattering

Elastic Scattering

Single Atoms:

$$I(\theta) \sim |f(\theta)|^2 = |f_0|^2 \cdot \frac{1}{(\theta^2 + \theta_0^2)^2}$$

$$\theta_0 = \frac{1}{2\pi(0.885a_0Z^{-1/3})}$$

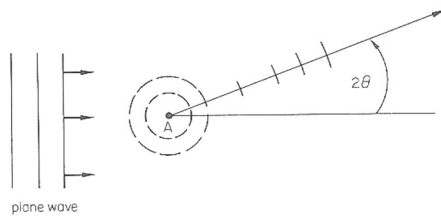


Figure 2.2 The scattering of a plane wave at an atom A through the formation of spherical wavelets travelling at an angle 2θ to the original direction of motion

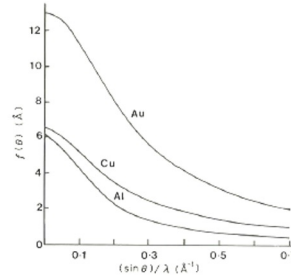


Fig. 2.2 Relationship between the atomic scattering factor $f(\theta)$ (in Å) and the scattering angle $(\sin \theta)/\lambda$ (in $\text{\AA}^{-1}$) for aluminium, copper and gold calculated using equation (2.1)

Scattering from an isolated atom in free space

15

15

Scattering from an collection of an amorphous collection of atoms
- neighboring atoms give rise to interference

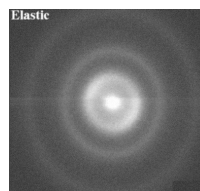
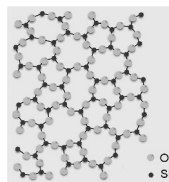
Amorphous Solids:

$$I(\theta) \sim |f(\theta)|^2 \cdot \left| 1 + \frac{\sin(\mathbf{kR})}{\mathbf{kR}} \right|$$

$$\mathbf{k} = \frac{4\pi}{\lambda} \sin(\theta)$$

R = Average Interatomic Spacing

Amorphous
Silica (SiO_2)



16

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Phonons:

$$I(\theta) \sim |f(\theta)|^2 \cdot \{1 - e^{-2M}\}$$

$$M = \frac{8\pi \langle u^2 \rangle \sin(\theta)}{\lambda}$$

Inelastic:

$$I(\theta) = \Gamma(\delta E, \theta) \cdot \frac{1}{\theta^2 + \theta_E^2}$$

$$\theta_E = \frac{\Delta E}{2\gamma_0 T_0} \quad \gamma_0 = \frac{1}{\sqrt{1-\beta^2}}$$

$\Gamma(\delta E, \theta)$: Imaginary Part of the Complex Dielectric constant(ϵ)
: Generalized Oscillator Strength

17

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Inelastic:

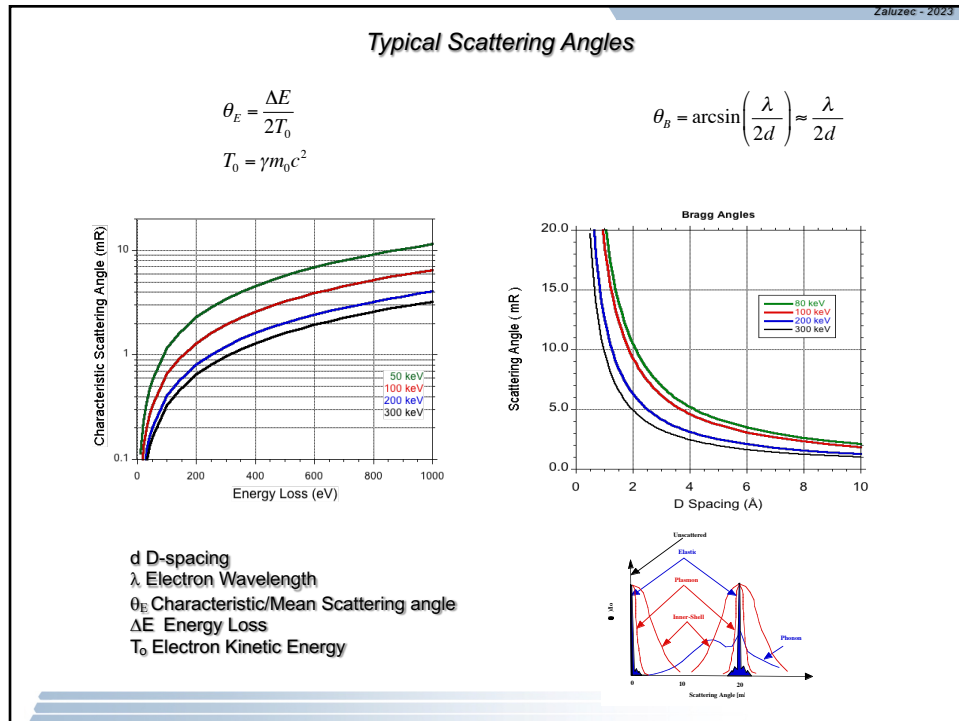
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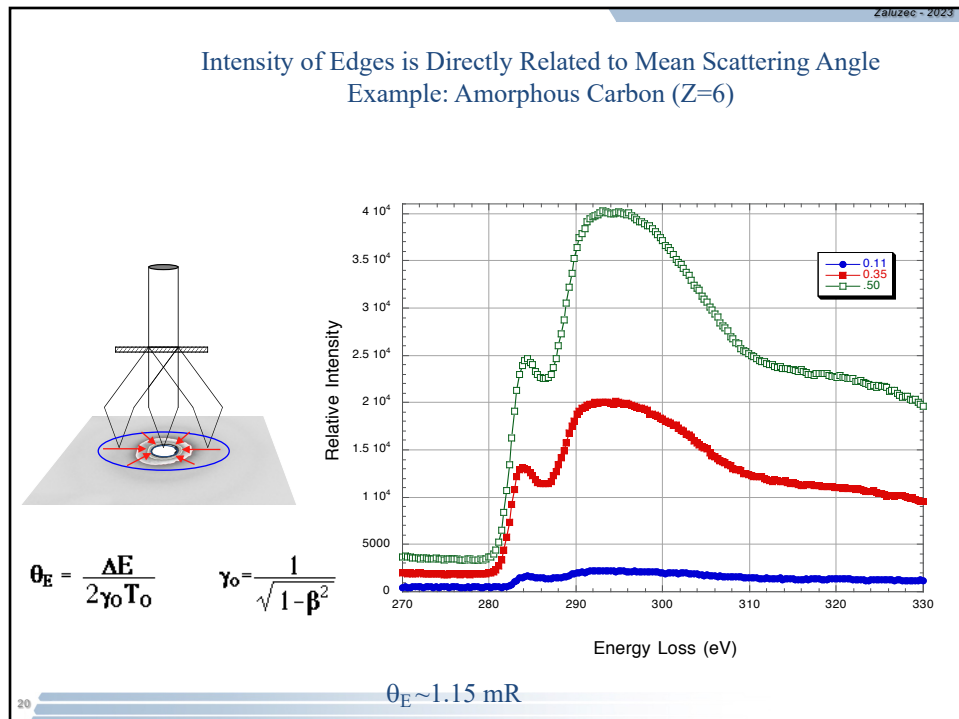
$\Gamma(\delta E, \theta)$: Imaginary Part of the Complex Dielectric constant(ϵ)
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18

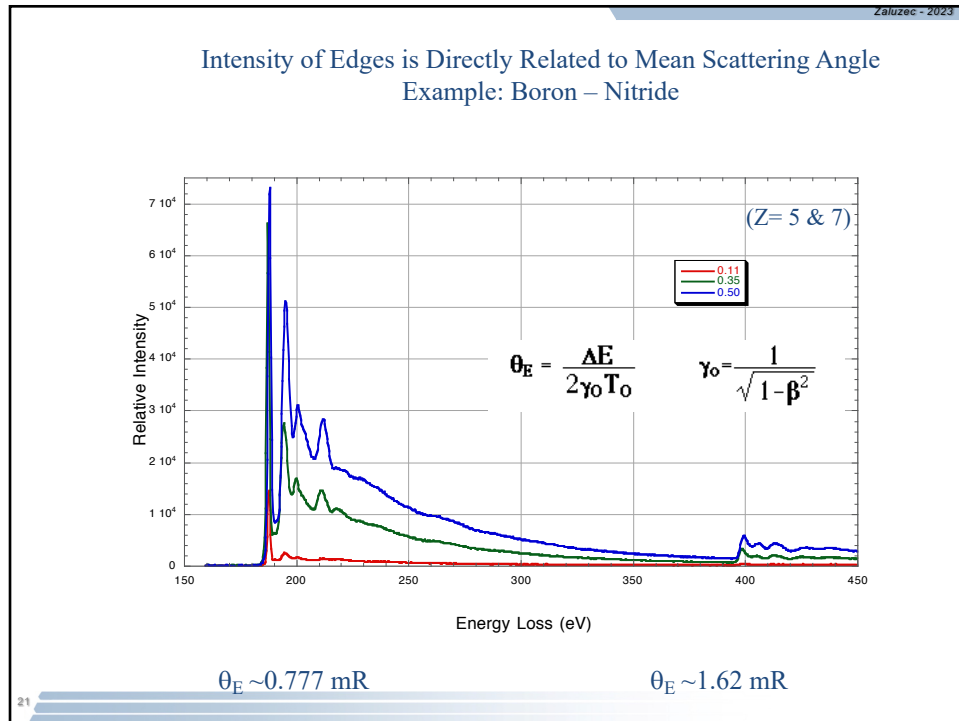
18



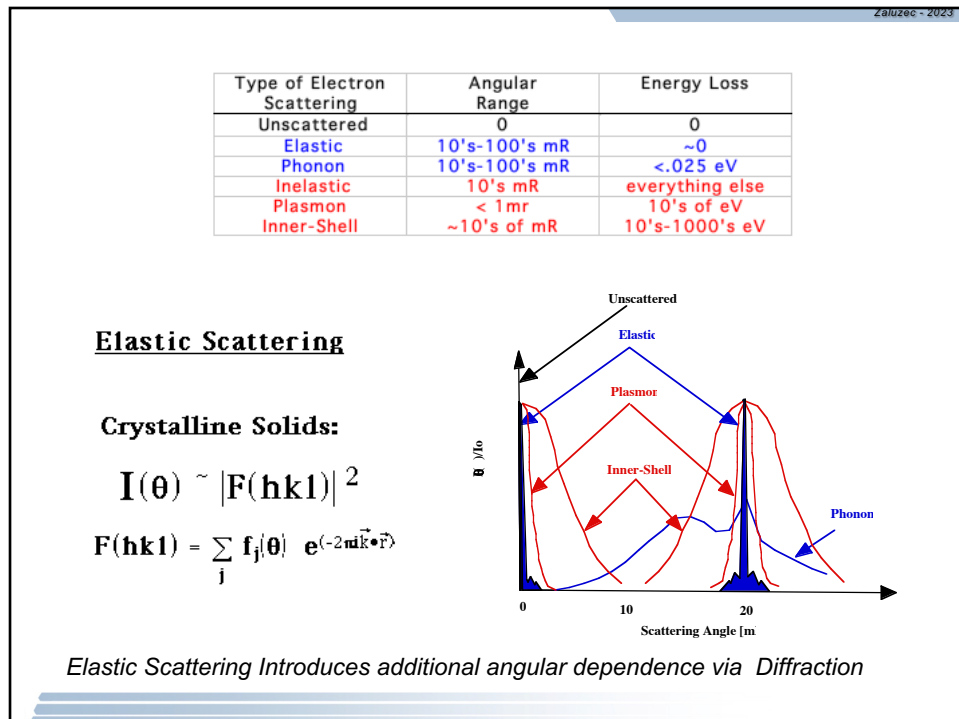
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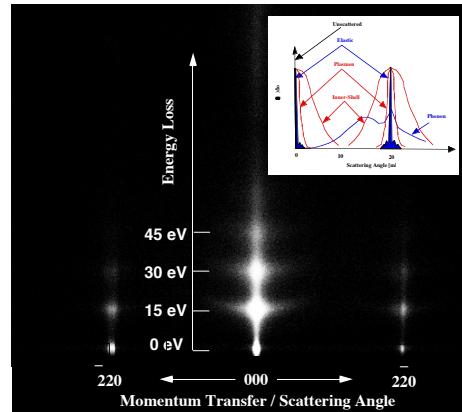
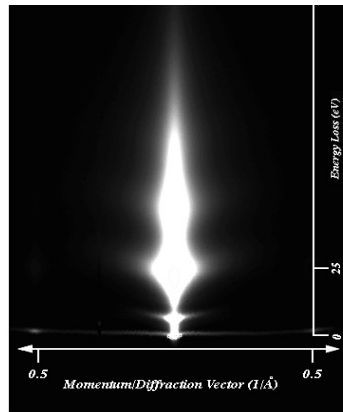


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Plasmon Dispersion Surfaces



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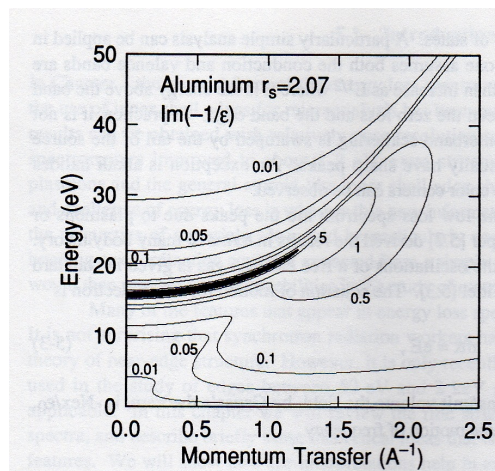
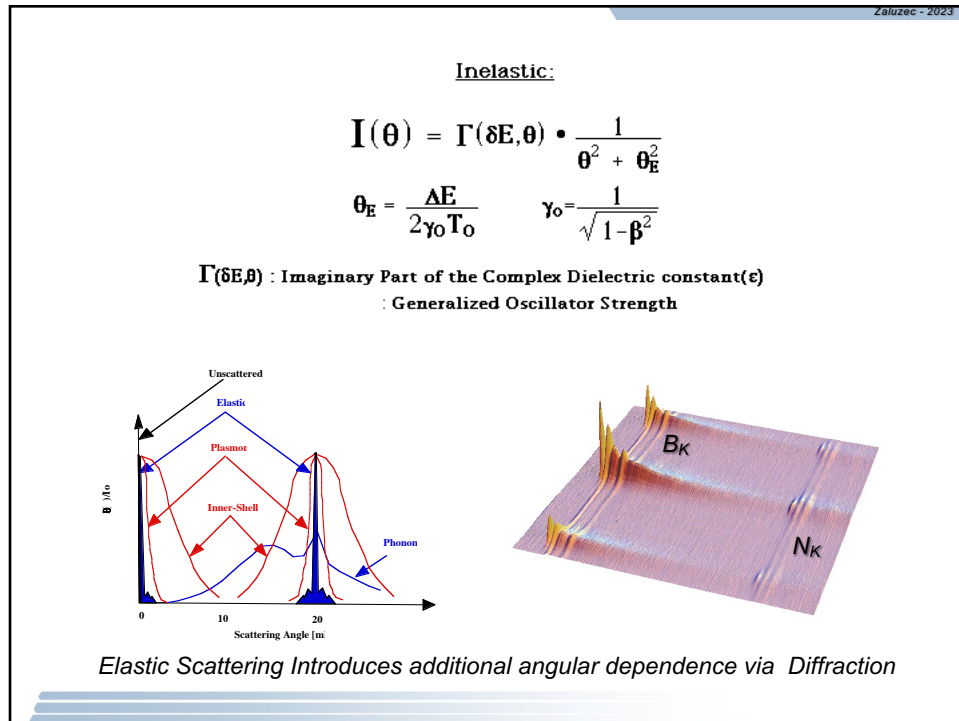
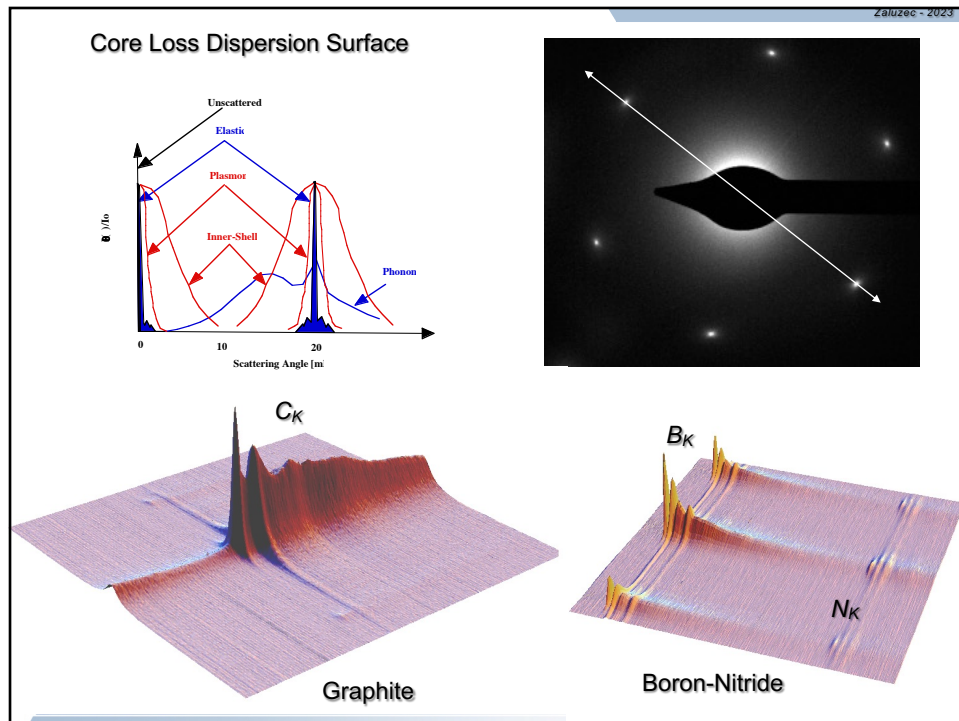


Figure 5-1. $\text{Im}[-1/\epsilon(q,\omega)]$ for aluminum showing the volume plasmon and its dispersion (change in energy as a function of momentum transfer, q) (Courtesy of P. E. Batson).

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Instrumentation: Detector Systems

Energy Loss Spectrometers
 Basic Principles
 Electrostatic/Electromagnetic
 Serial/Parallel Detector Systems
 Spectral Artifacts
 Multichannel Analyzers

27

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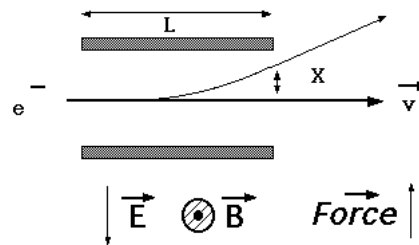
Force (F) and displacements (X) on electrons by different types of fields yields a deflection in their trajectory. In a uniform field region the electrons drift at a characteristic radius (R).

Electrostatic

$$\vec{F}_E = q \vec{E} \quad X_E = \frac{1}{2} \frac{qEL^2}{m_0 v^2} \quad R_E = \frac{m_0 v^2}{qE}$$

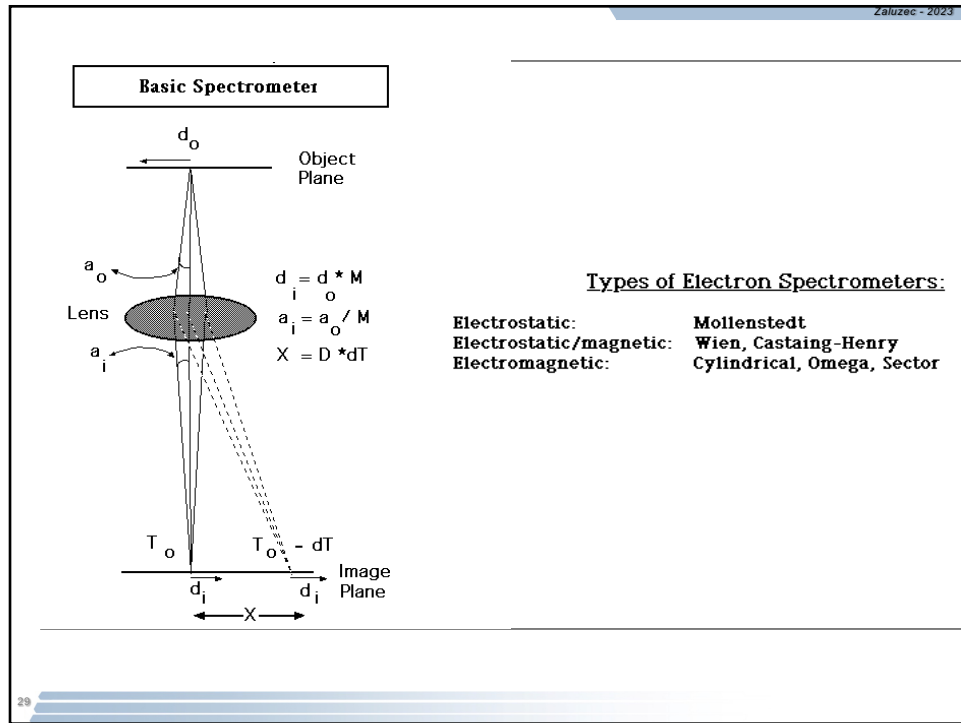
Electromagnetic

$$\vec{F}_B = q [\vec{v} \times \vec{B}] \quad X_B = \frac{1}{2} \frac{qBL^2}{m_0 v} \quad R_B = \frac{m_0 v}{qB}$$

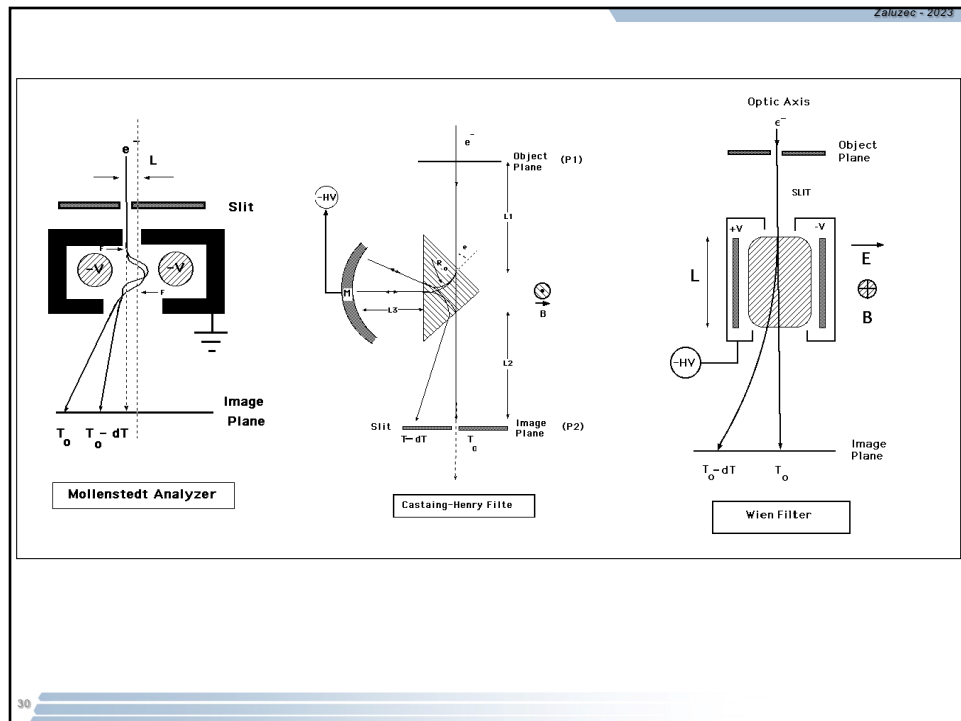


28

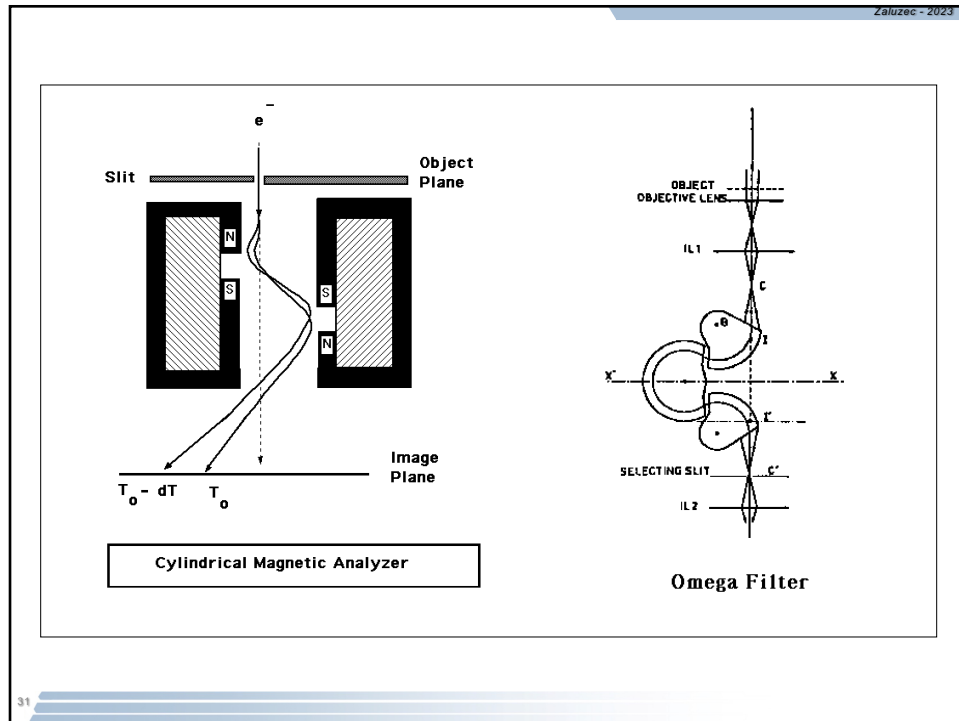
28



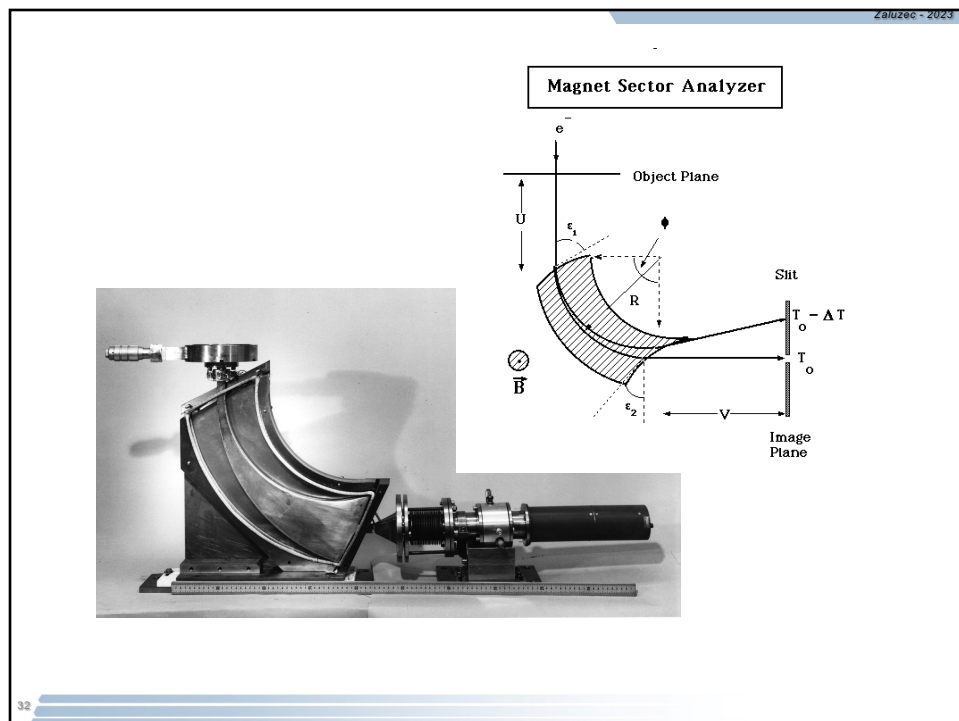
29



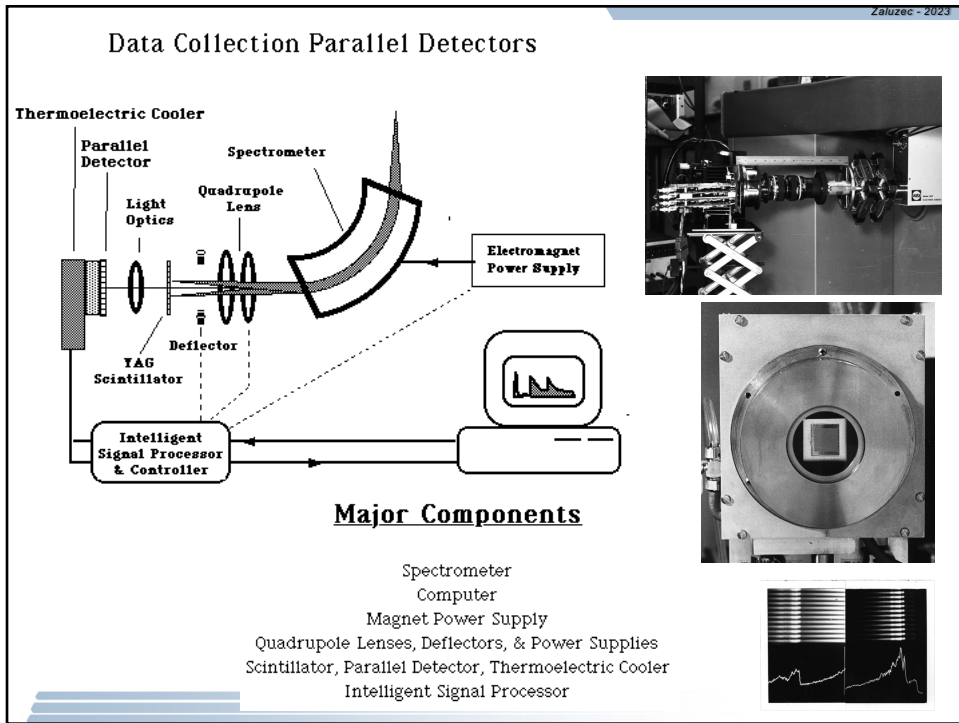
30



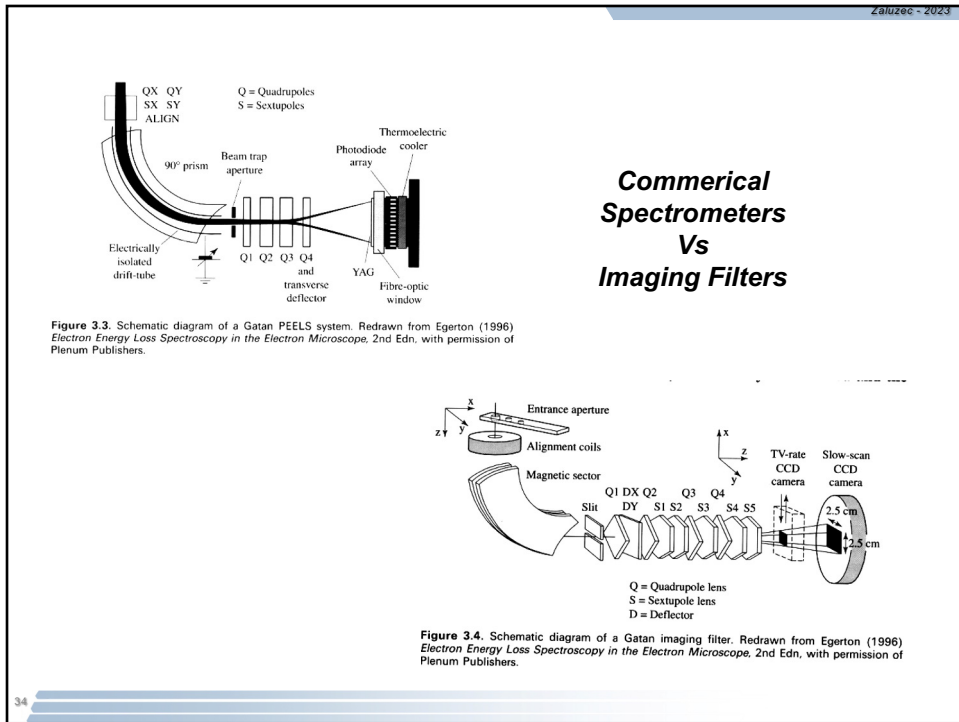
31



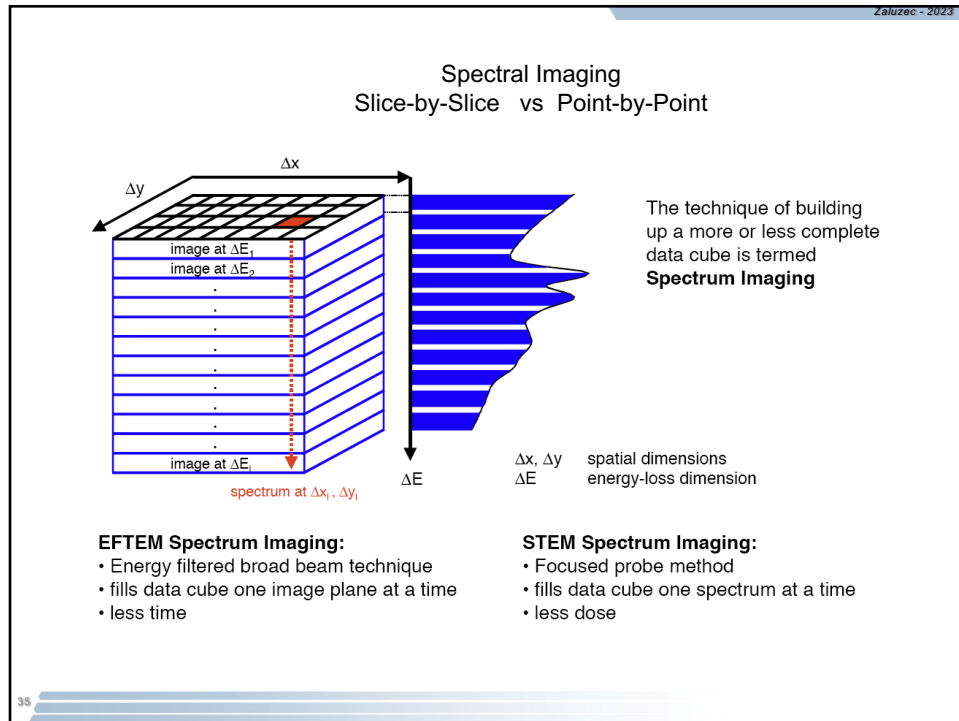
32



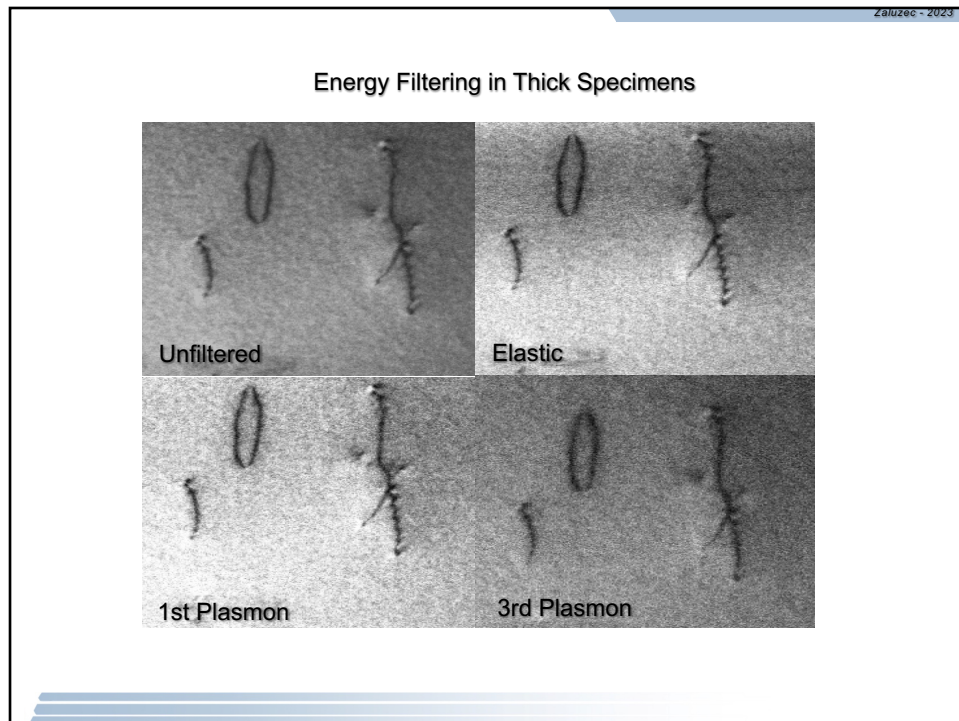
33



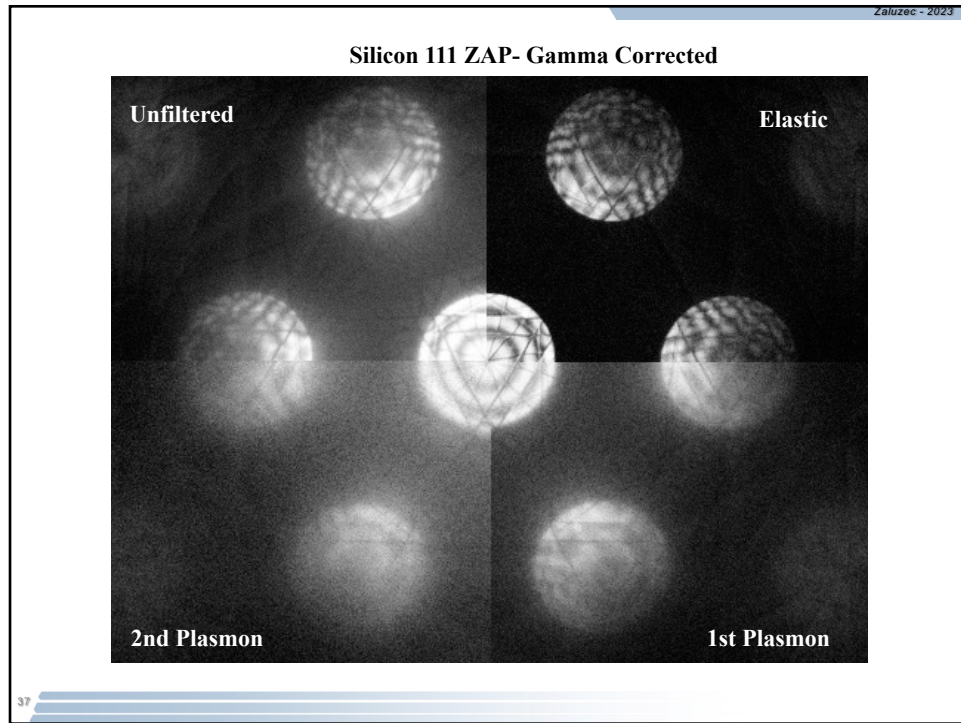
34



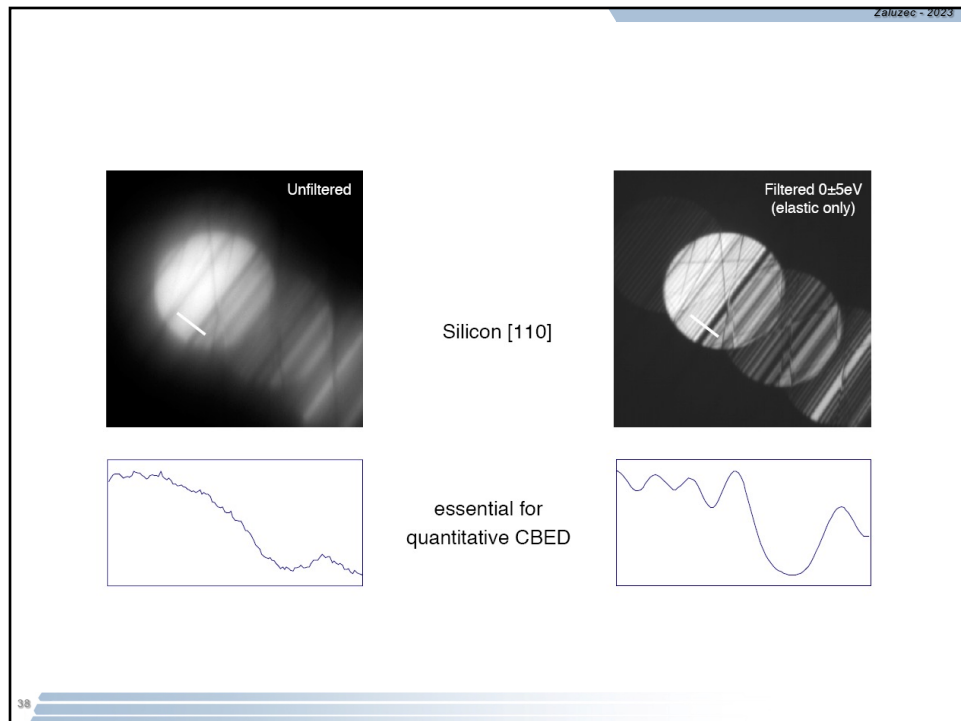
35



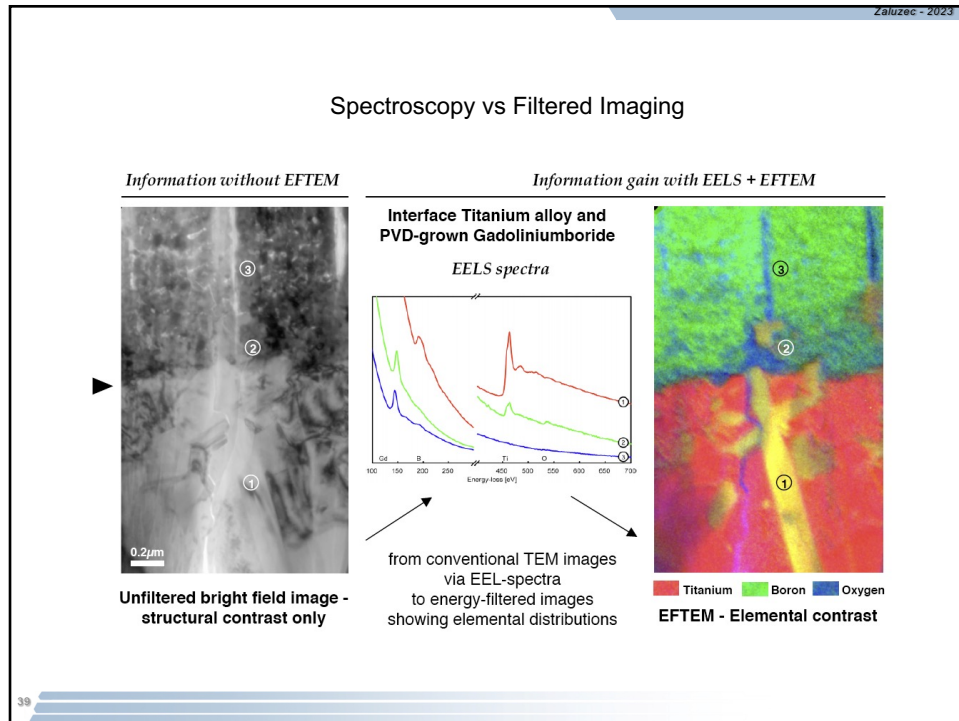
36



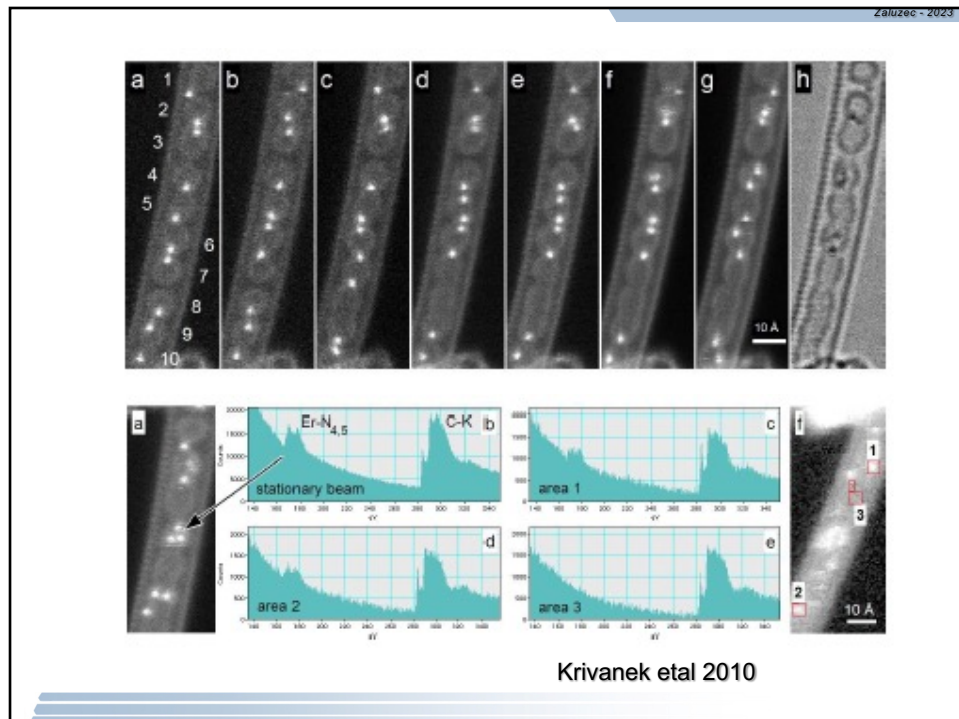
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What is the Goal of the EELS Experiment

- Detection
- Quantification
- Filtering (Elastic vs Inelastic Signal)
- Spatial Distribution (HyperSpectral Imaging)
- High Resolution Spectroscopy ...

41

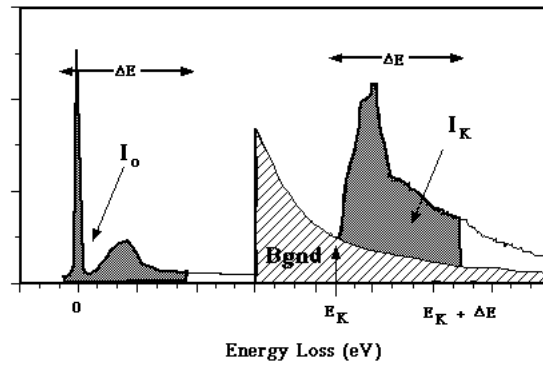
Data Analysis and Quantification:

Spectral Processing
Thin Film Quantification Methods
Specimen Thickness Effects

42

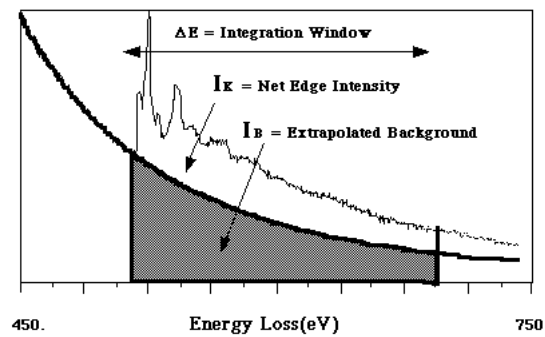
42

Measurement of Parameters required for EELS Quantification



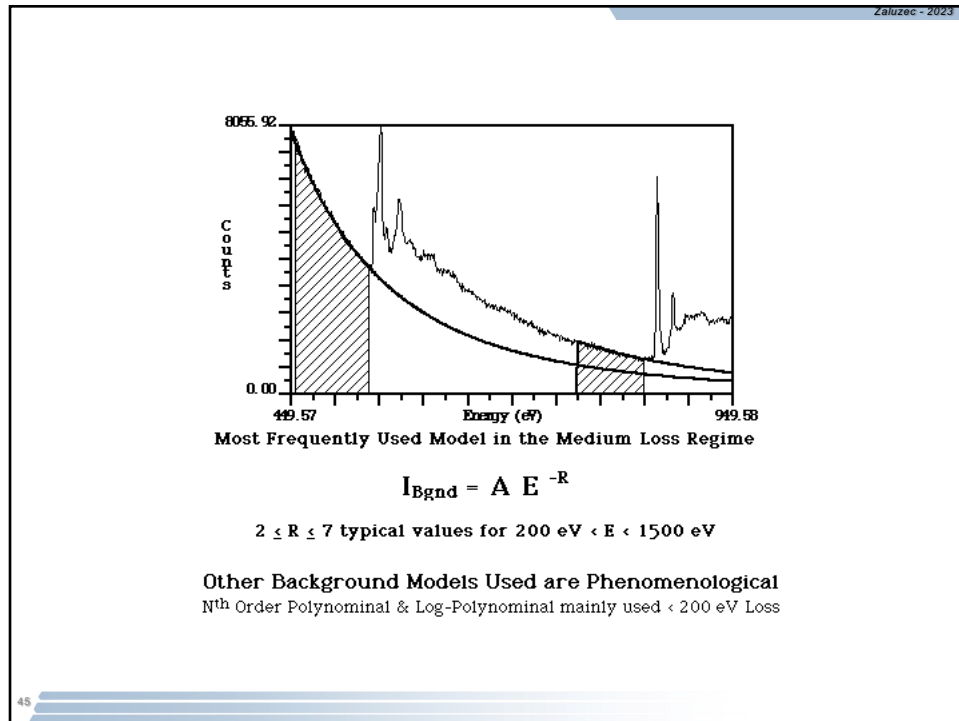
43

43

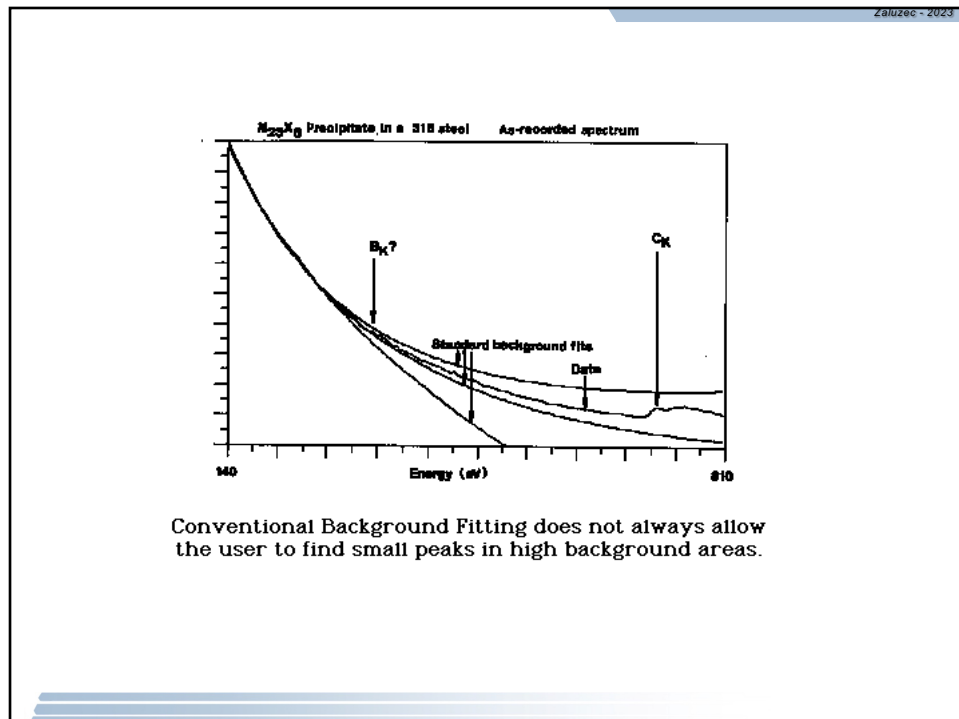


44

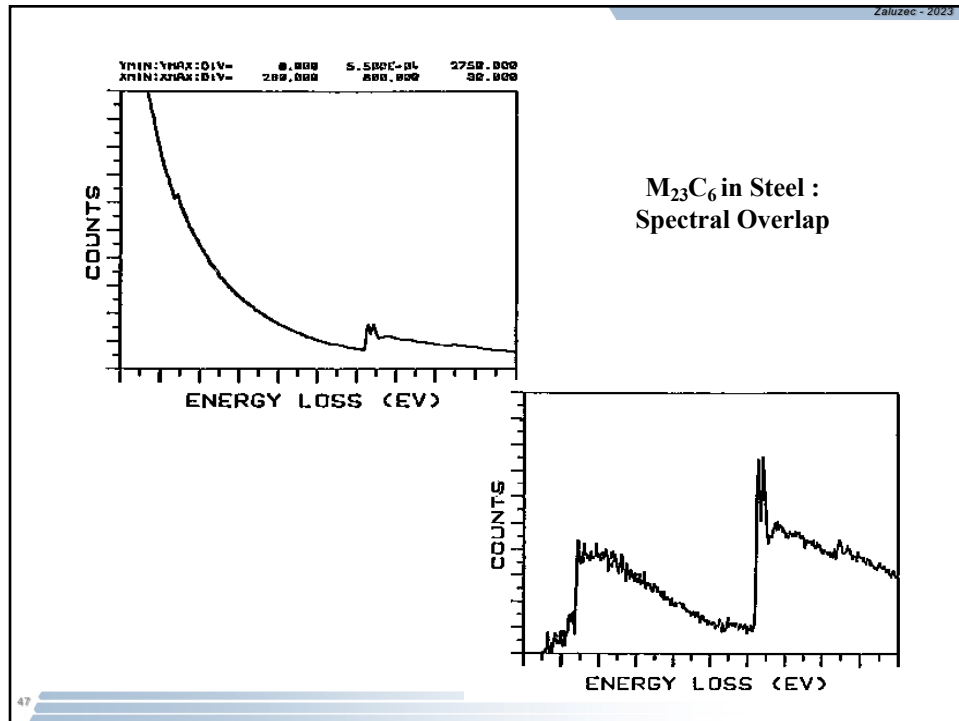
44



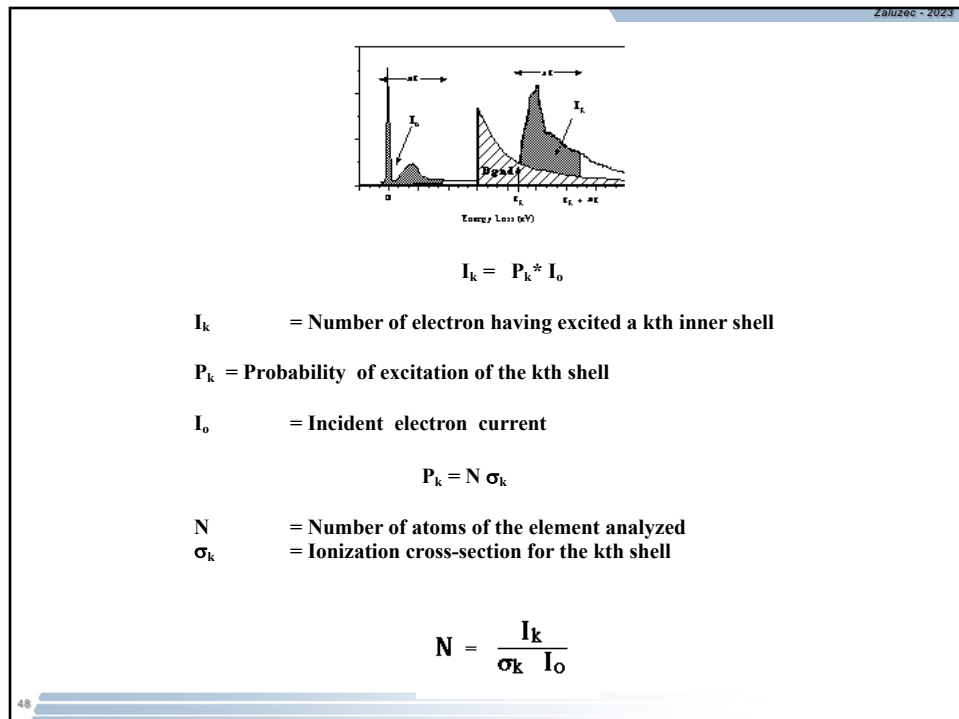
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46



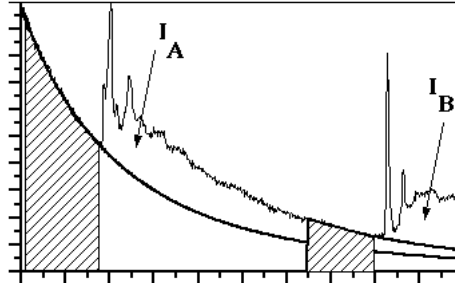
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48

Alternatively;

Consider the ratio of Intensities of any two Edges in the same spectrum I_A and I_B



Invoke the Ratio Method and obtain the exact equation:

$$\frac{I_A}{I_B} = \frac{\sigma_A}{\sigma_B} \frac{N_A}{N_B}$$

Note the similarity of this equation with that of Thin Film XEDS

49

49

But in the real world the assumptions used in the above simple arguments are never realized:

- Measure all scattered electrons ($\beta=180^\circ$)
- Integration over all energy Losses

Because we must measure over a finite energy window (δE) we modify the expression to:

$$N_A = \frac{I_A(\delta E)}{\sigma_A(\delta E) \cdot I_0}$$

we also measure over a finite angular window (β) and therefore, we modify the expression to:

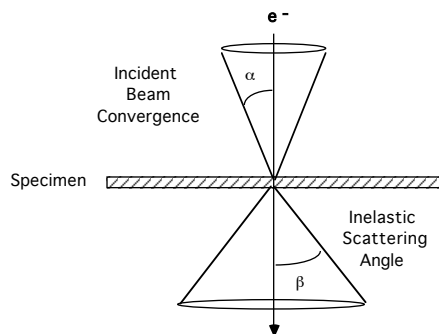
$$N_A = \frac{I_A(\delta E, \beta)}{\sigma_A(\delta E, \beta) \cdot I_0}$$

and the ratio equation becomes:

$$\frac{N_A}{N_B} = k_{AB} \frac{I_A(\delta E, \beta)}{I_B(\delta E, \beta)}$$

with

$$k_{AB} = \frac{\sigma_B(\delta E, \beta)}{\sigma_A(\delta E, \beta)}$$



50

50

By measuring $\mathcal{N}$ edges we have $\mathcal{N}-1$ equations, if we invoke the argument that the compositions must sum to unity

$$\sum_{i=1}^{\mathcal{N}} C_i = 1$$

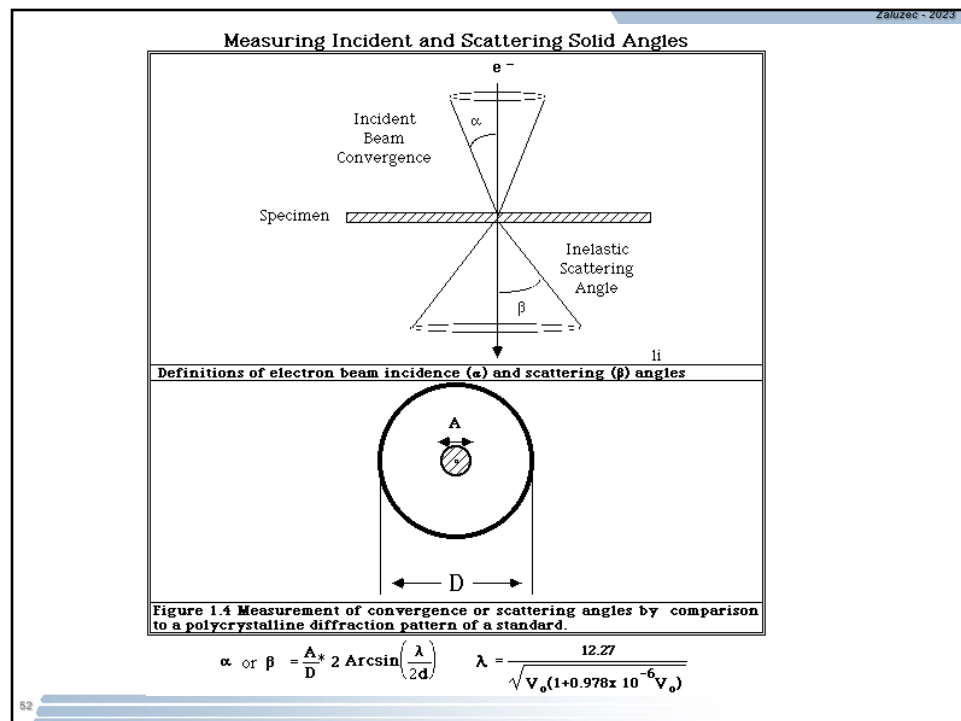
we arrive at a set of $\mathcal{N}$ equations and $\mathcal{N}$ unknowns which can be solved by simple algebra.

For example:

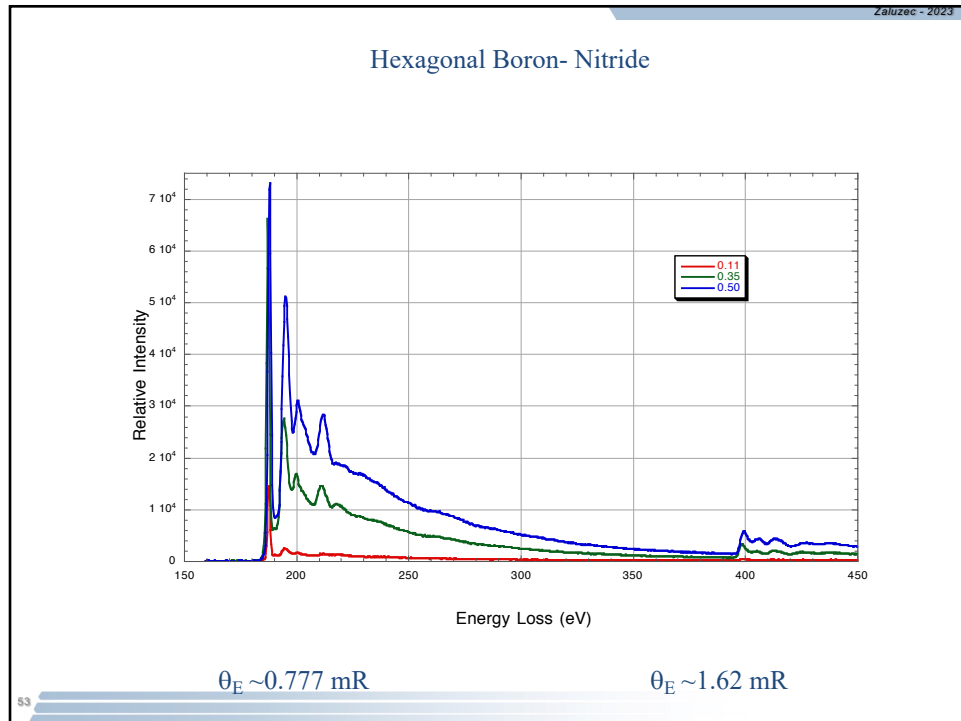
- if $N_A/N_B = 2$; then $N_A = 2 N_B$
- if $N_A + N_B = 1$; then $3N_B = 1$ or $N_B = 0.33$
- and $N_A = 1 - N_B = 0.67$

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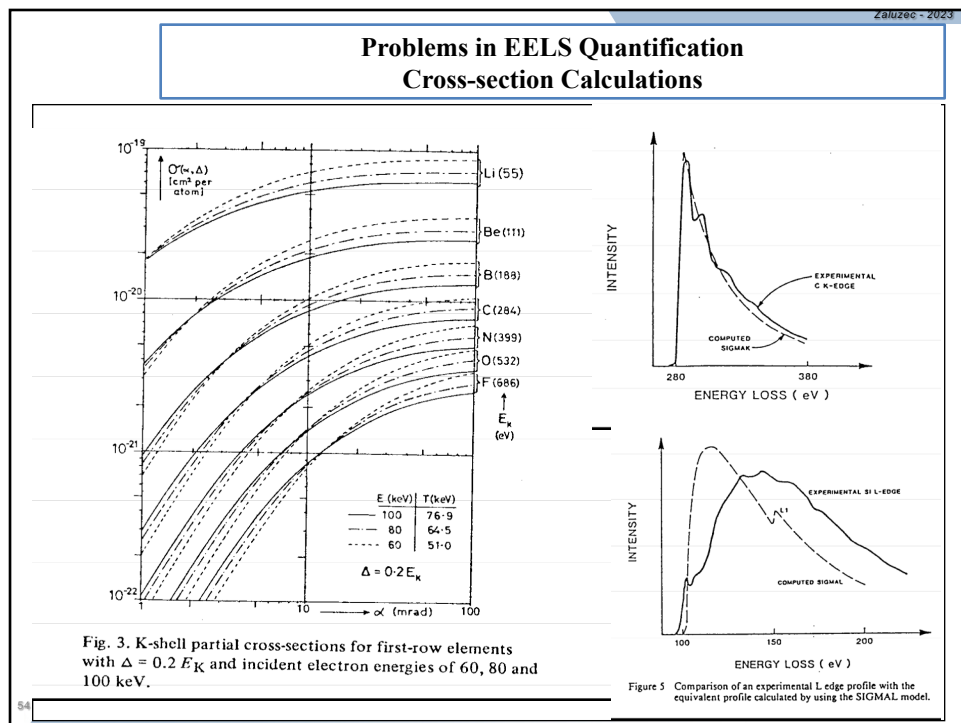
51



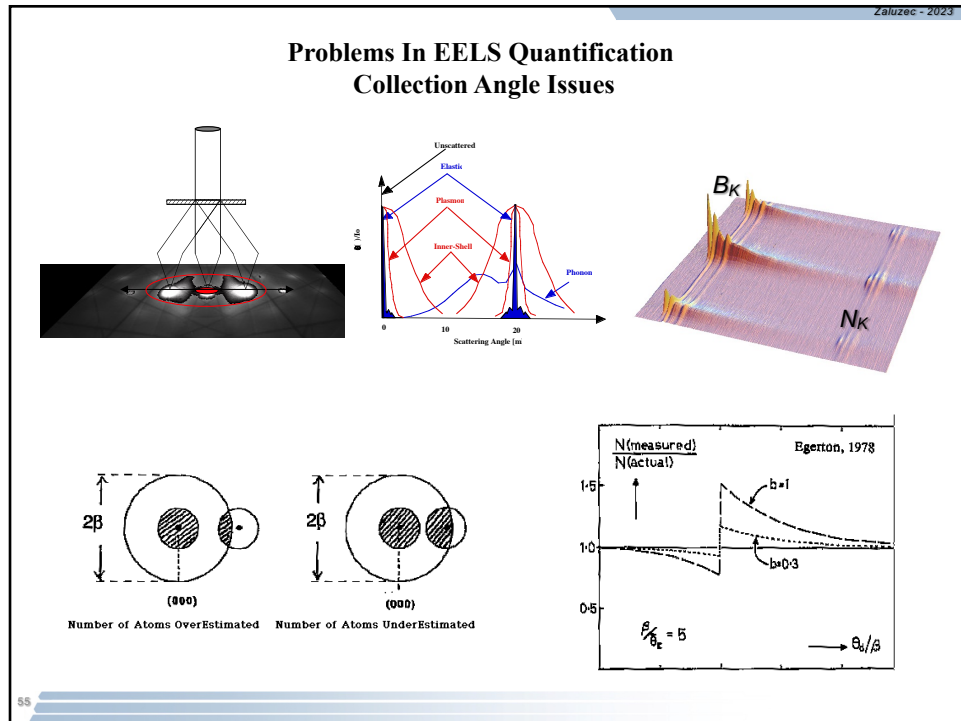
52



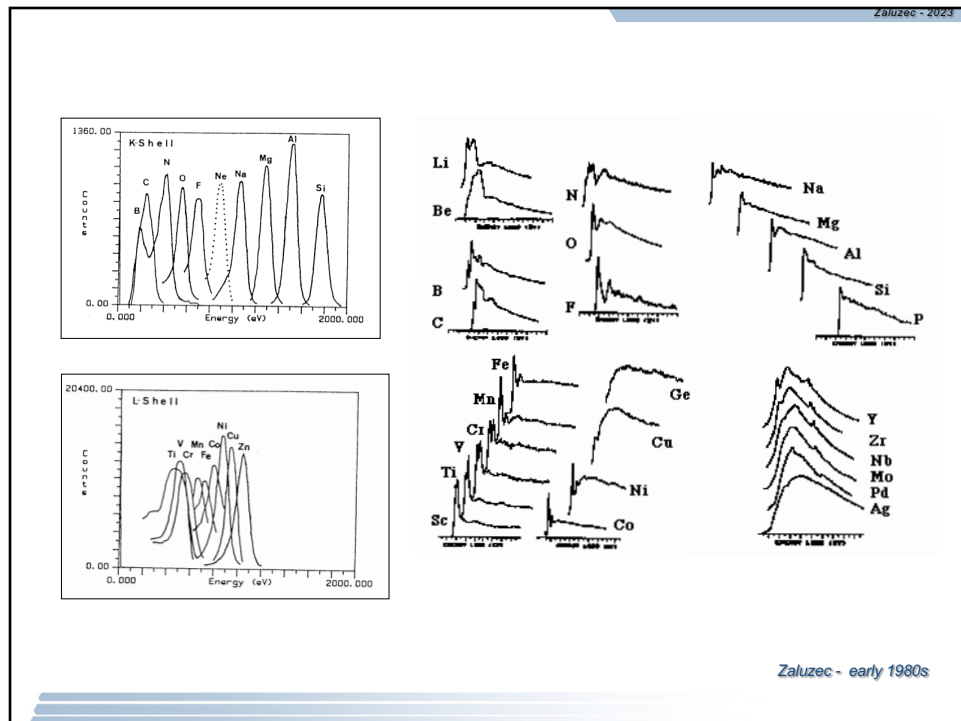
53



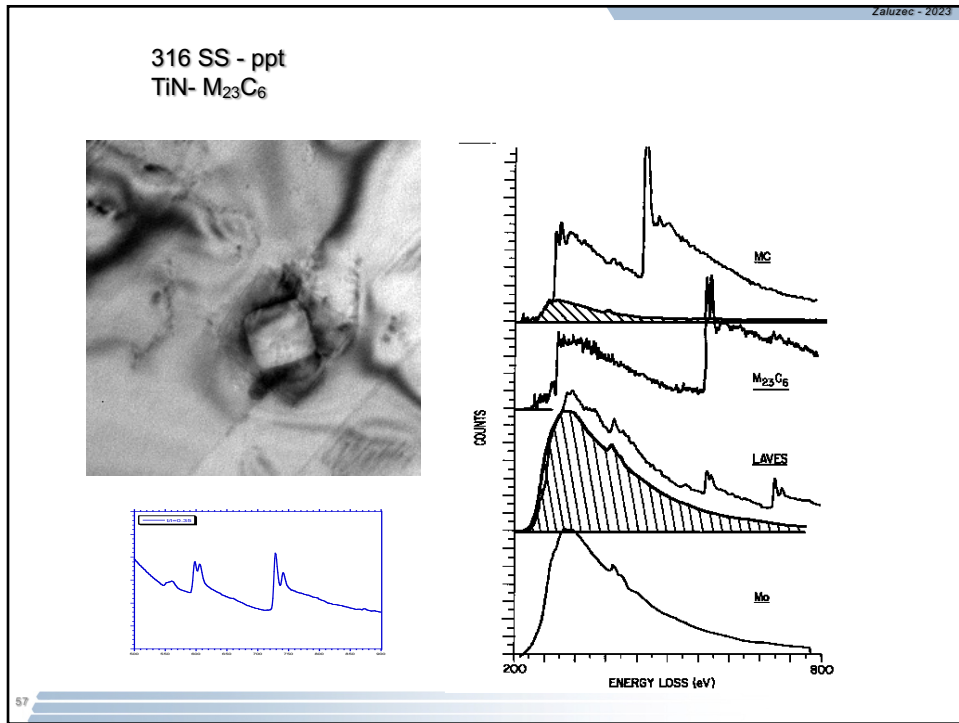
54



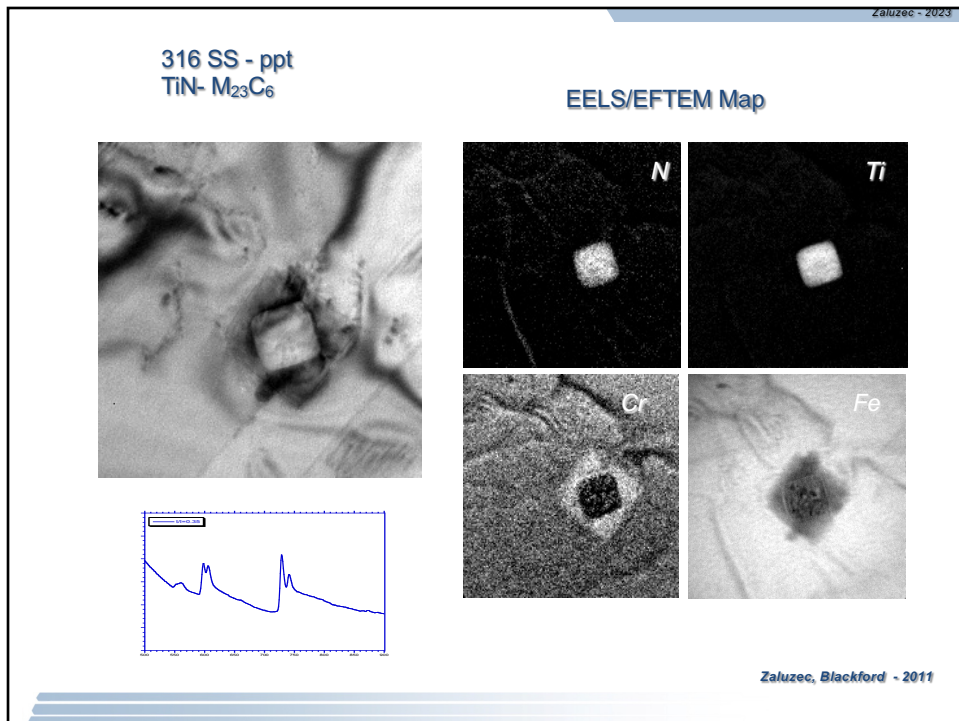
55



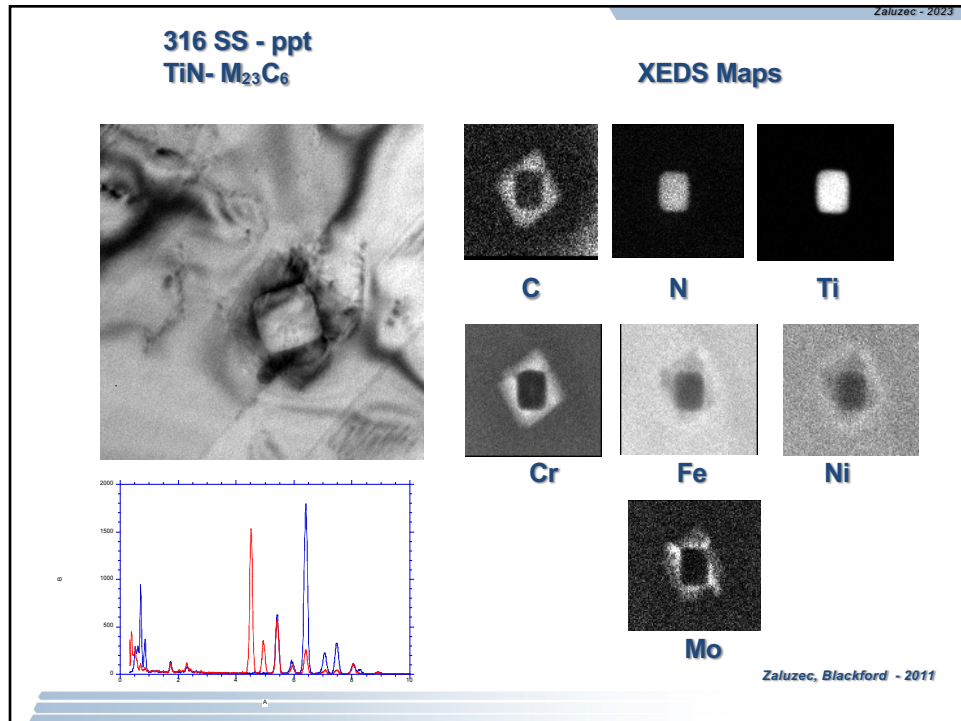
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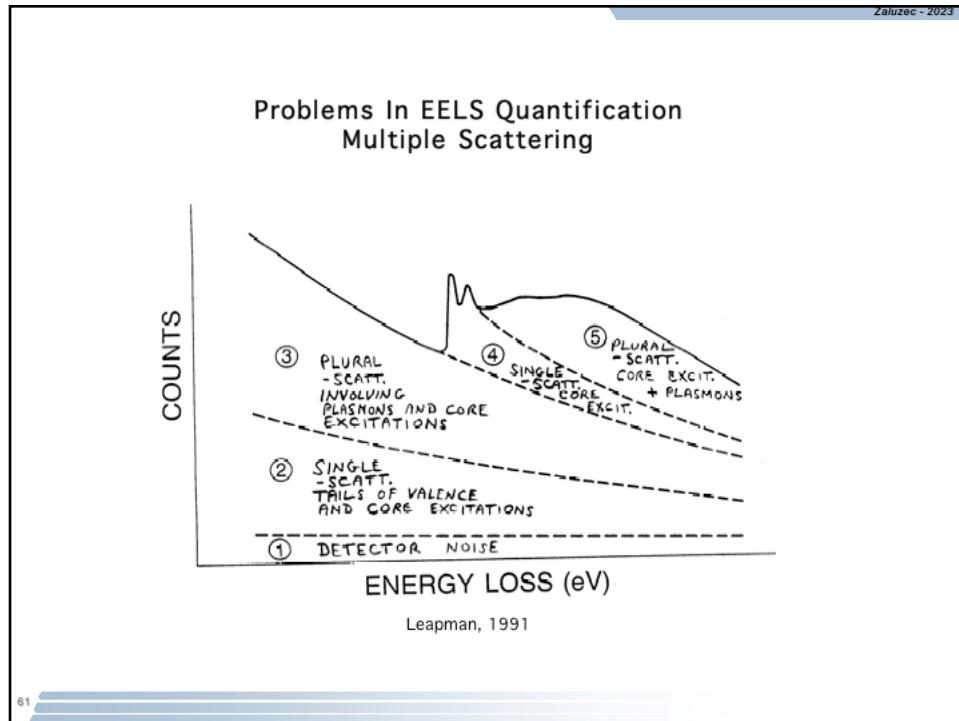
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Effects of Specimen Thickness

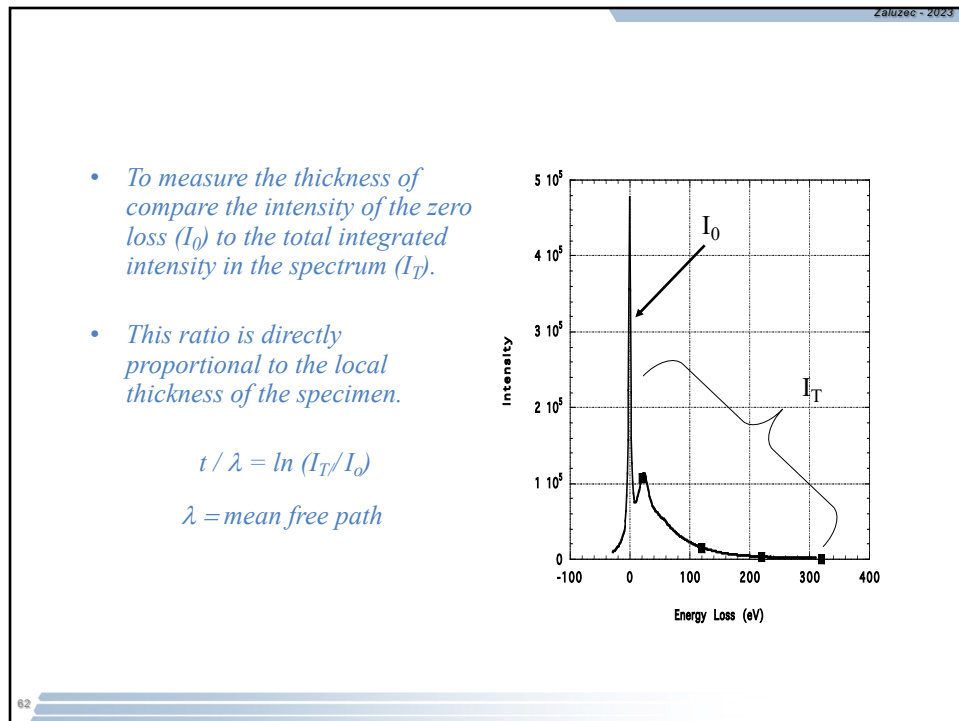
- Multiple Scattering
 - Low Loss
 - Core Loss -Visibility
 - Quantification Effects

60

60



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62

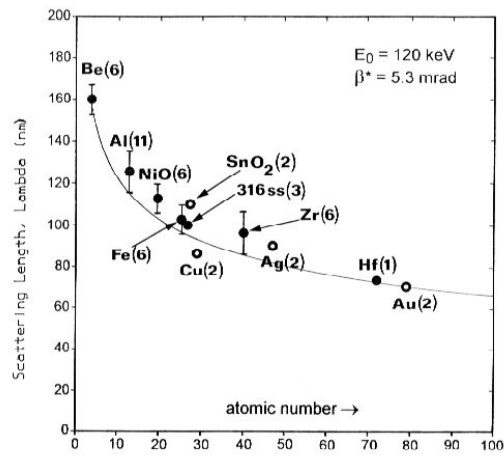
Inelastic MFP:

$$\lambda = 106 F (E_0/E_m) / \ln(2\beta E_0/E_m)$$

λ in nm,
 β in mrad,
 E_0 in keV
 E_m in eV

$$E_m = 7.6Z^{0.36}$$

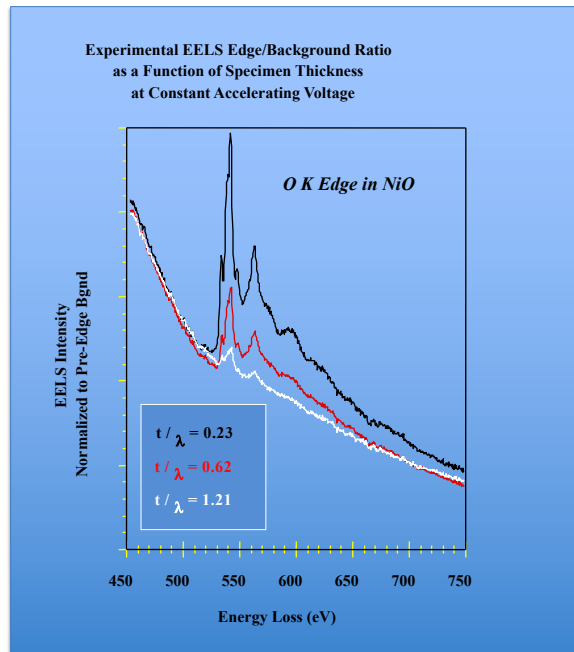
$$F = (1 + E_0/1022\text{keV}) / (1 + E_0/511\text{keV})^2$$



(Malis et al., JEMT 1988)

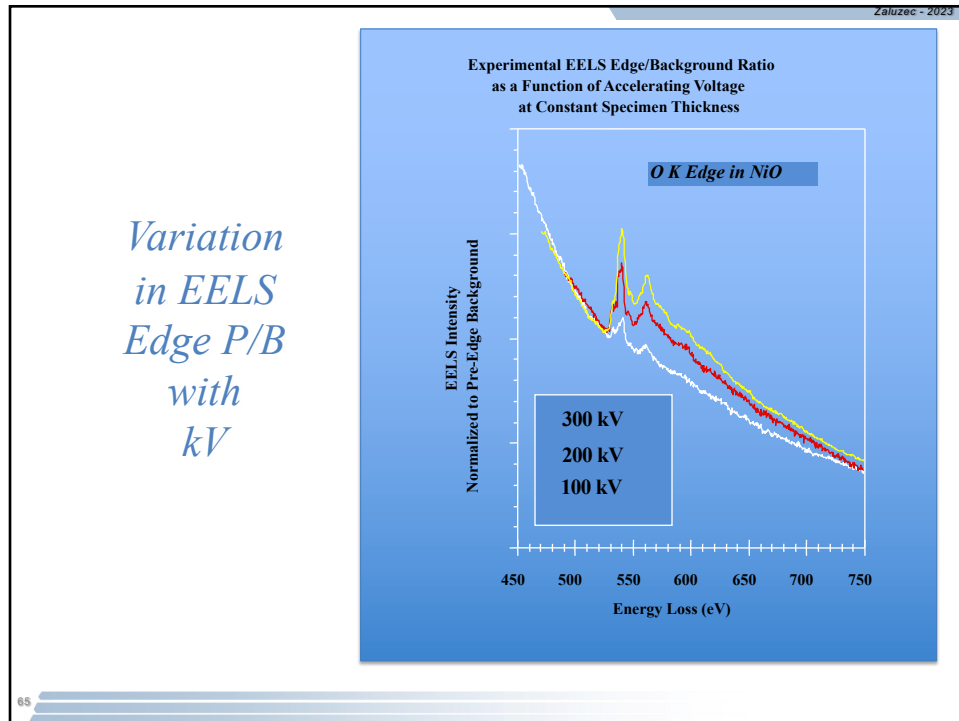
63

*Variation
in EELS
Edge P/B
with
Thickness*

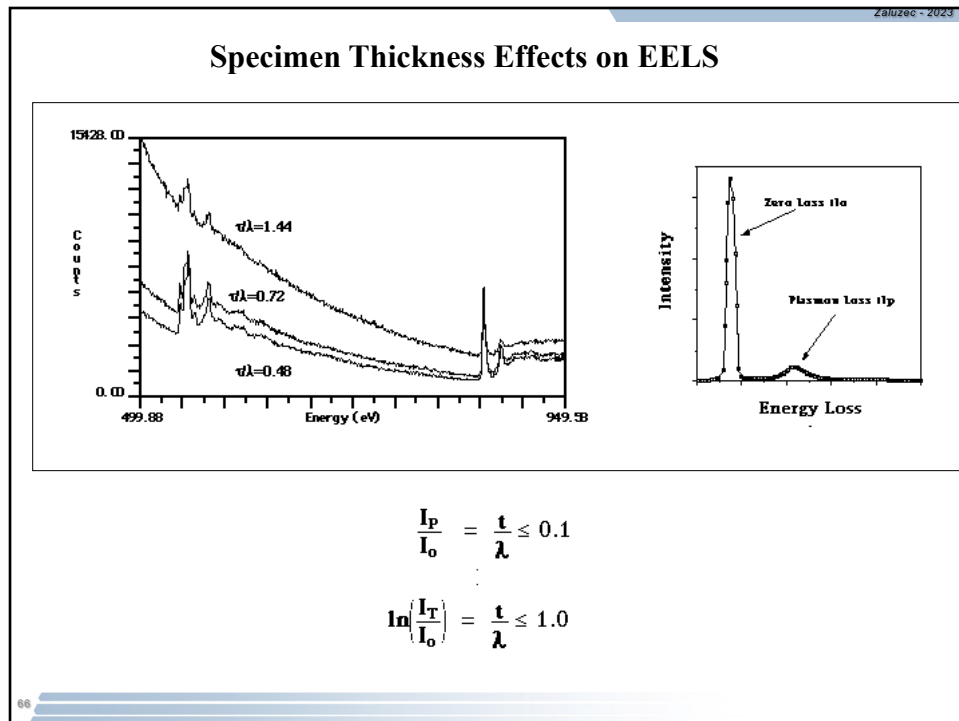


64

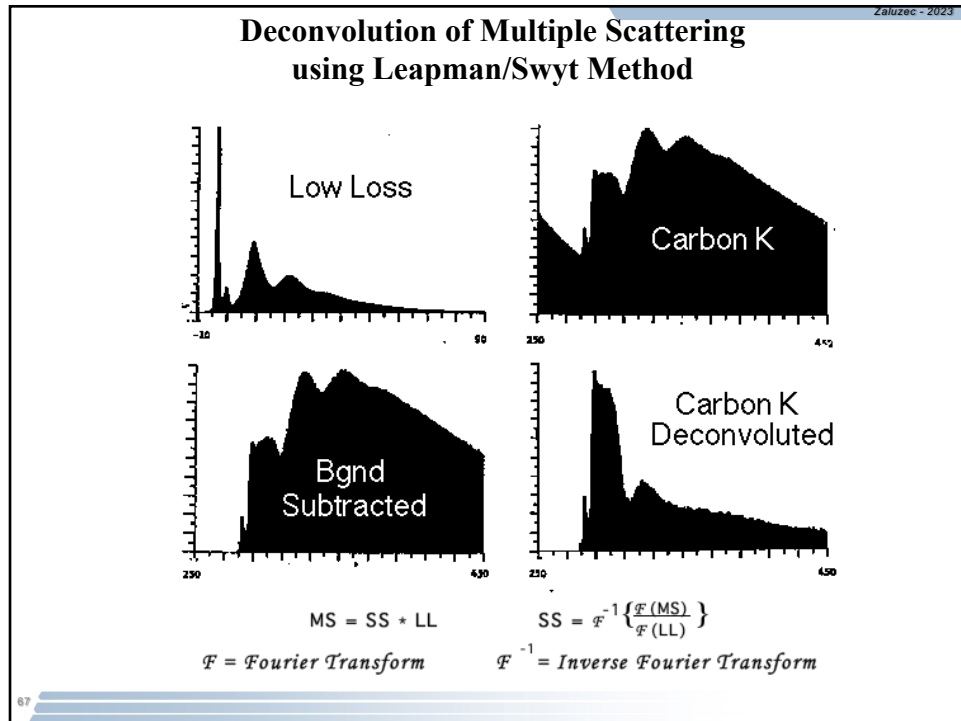
64



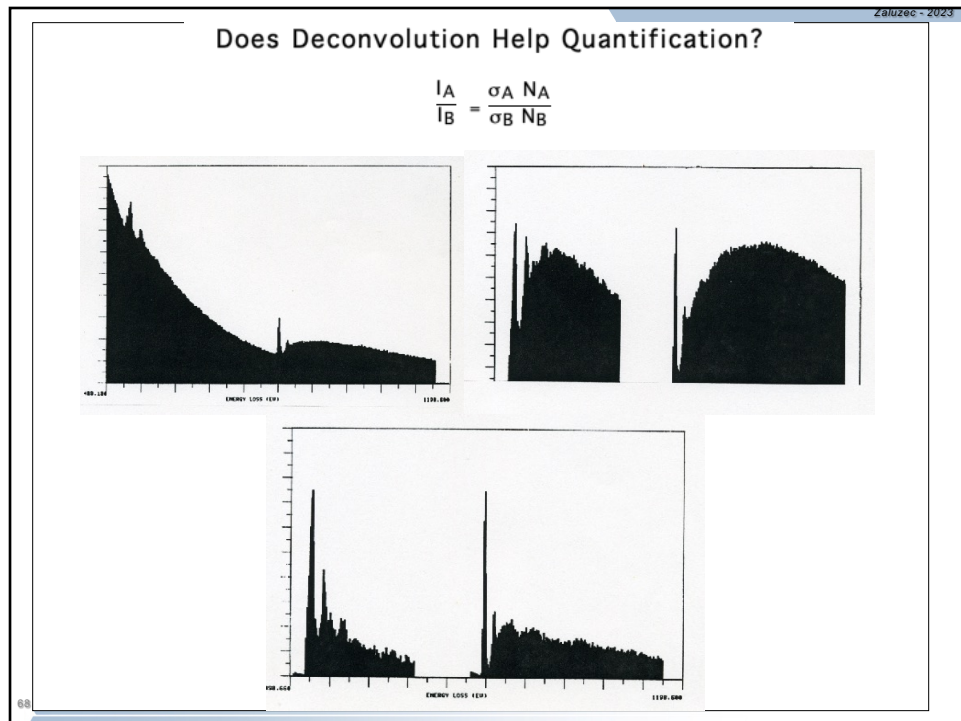
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67



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Does Deconvolution Help Quantification?

$$\frac{I_A}{I_B} = \frac{\sigma_A N_A}{\sigma_B N_B}$$

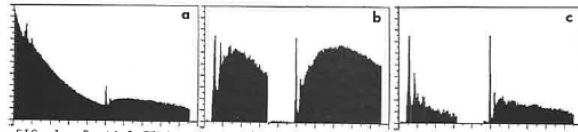
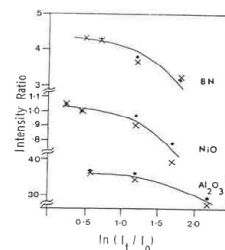
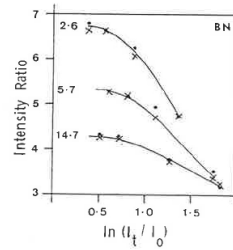


FIG. 1.--Partial EELS Spectrum (500-1200 eV) from NiO specimen: 100 keV, 5.7 mrad scattering angle, a) unprocessed data b) background stripped, c) deconvoluted.

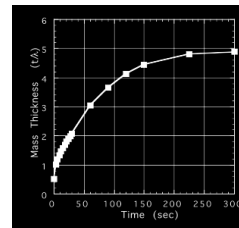
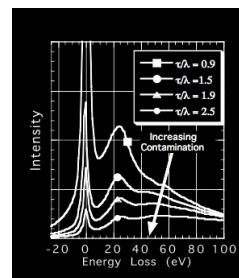
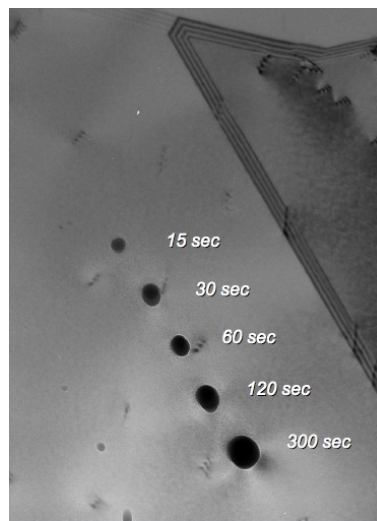


This defines a "Thin Film Approximation" for EELS i.e. $\frac{t}{\lambda} < 1.0$

69

69

Contamination Effects on EELS



70

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Spectral Imaging Slice-by-Slice vs Point-by-Point

The technique of building up a more or less complete data cube is termed **Spectrum Imaging**

$\Delta x, \Delta y$ spatial dimensions
 ΔE energy-loss dimension

EFTEM Spectrum Imaging:

- Energy filtered broad beam technique
- fills data cube one image plane at a time
- less time

STEM Spectrum Imaging:

- Focused probe method
- fills data cube one spectrum at a time
- less dose

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Elemental Mapping

Determine and subtract edge background using two pre-edge images to obtain the true edge signal

- Minimum of two background windows are necessary
- Map intensity is directly proportional to projected concentration
- Map-intensity can be related to absolute concentration if thickness and elemental cross-sections are known

Gatan Digital Micrograph

72

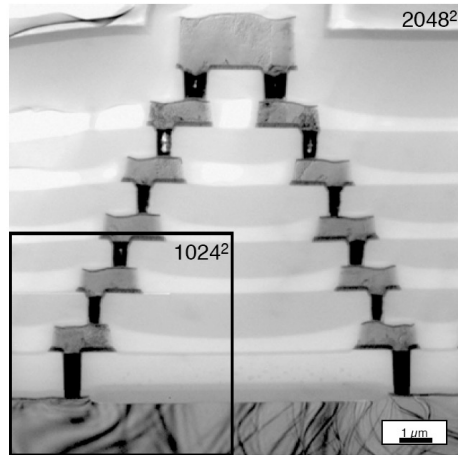
72

Elemental Mapping

6 layer metallization
test structure

recorded on a CM200, LaB6
with a GIF2002 (2K CCD)

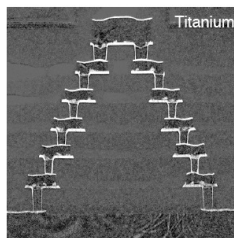
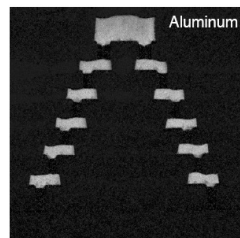
field of view: $12\ \mu\text{m}$
number of pixels: 4.2×10^6



Gerald Kothleitner

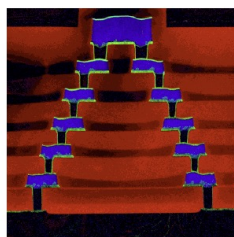
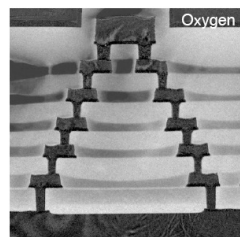
73

73



3 images each around:

O K edge: @ 532 eV
Ti L₂₃ edge: @ 455 eV
Al K edge: @ 1560 eV



■ O ■ Ti ■ Al

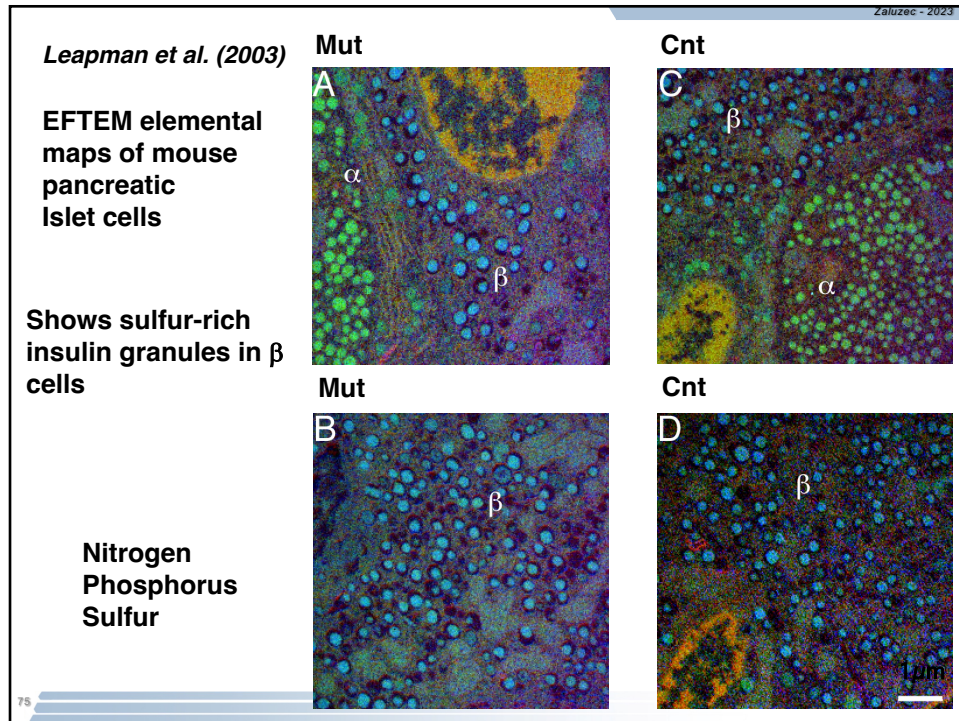
Color overlays, RGB images:

- assign a color to each elemental map: O red, Ti green and Al blue
- superimpose three color layers to form RGB composite

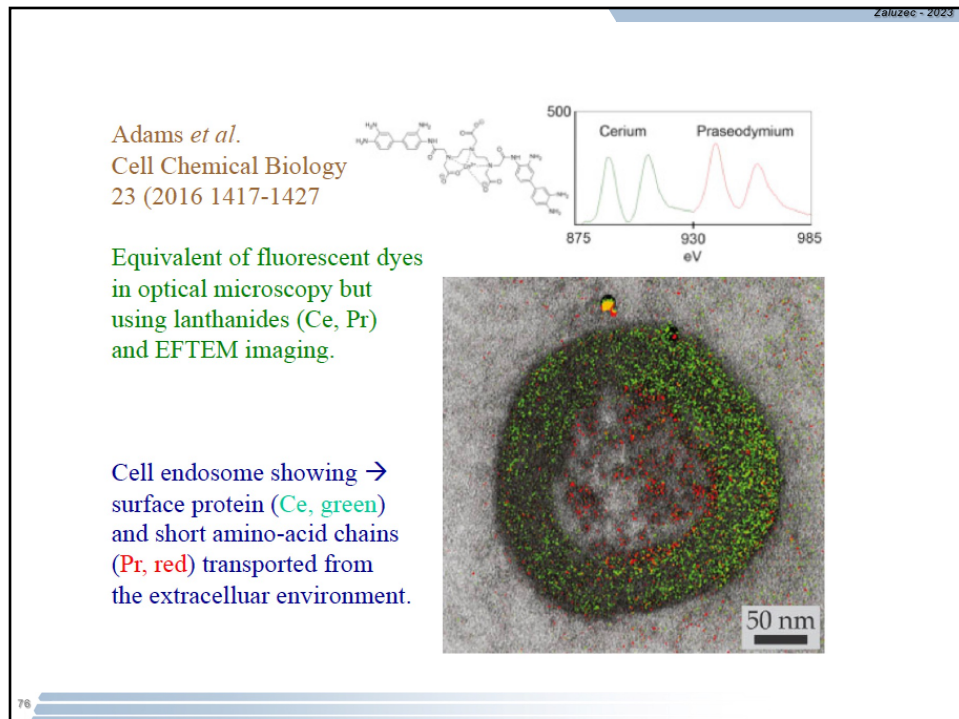
Gerald Kothleitner

74

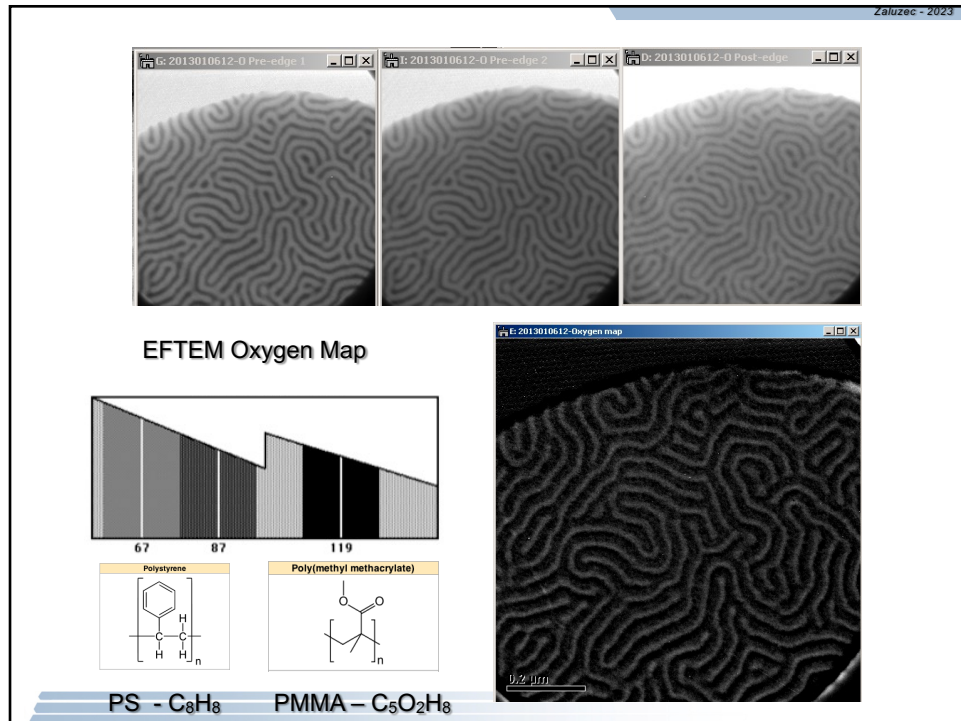
74



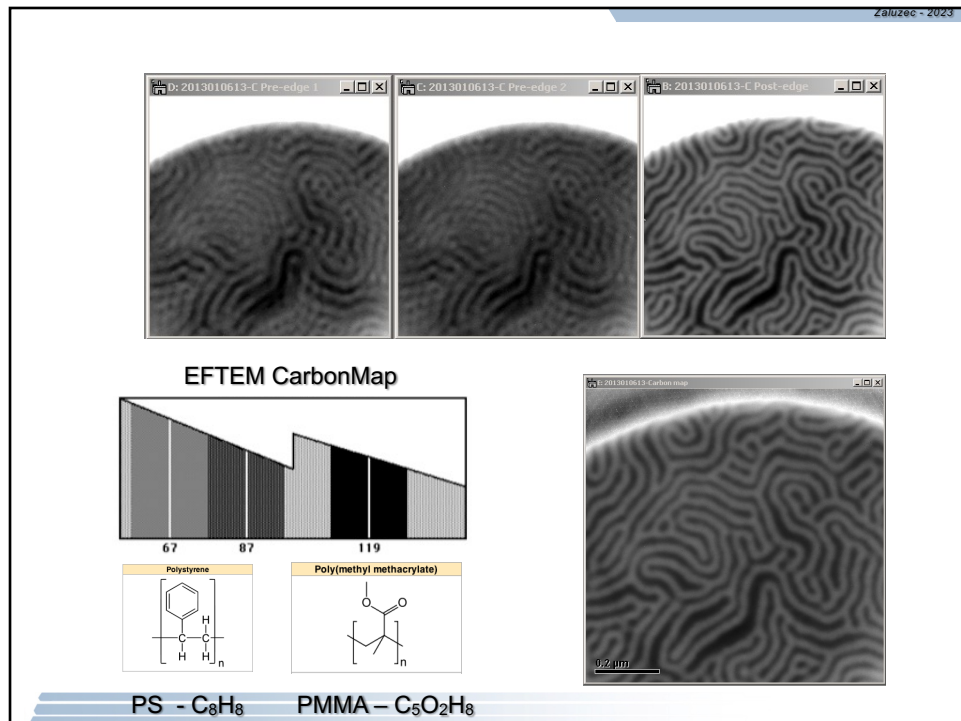
75



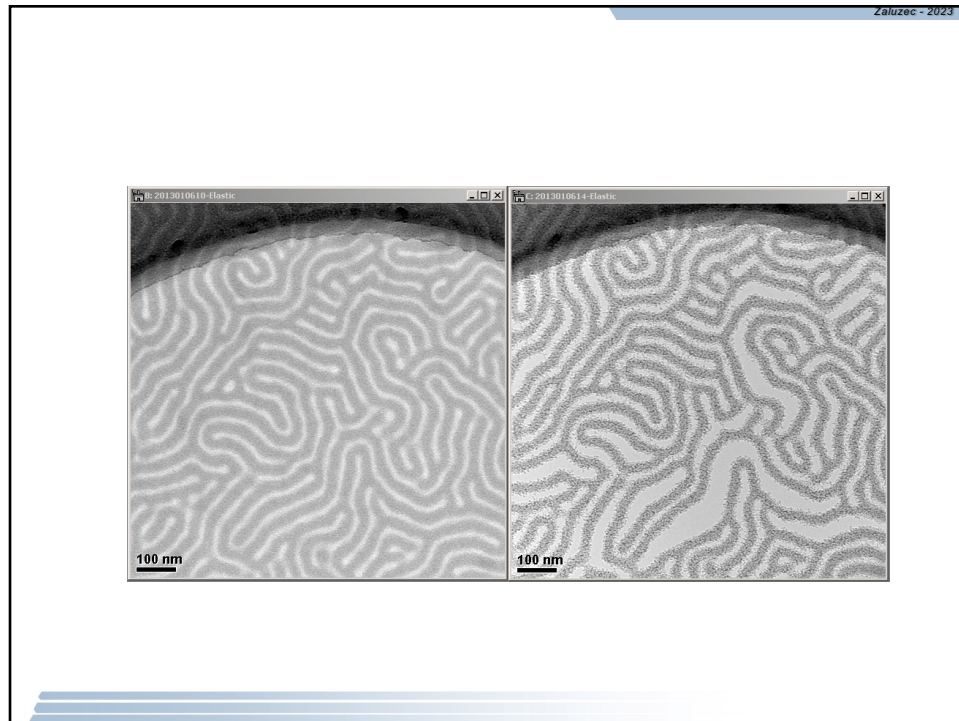
76



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Steps in Quantitative (Elemental) Analysis

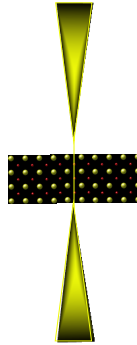
- Select the operating mode: Is it appropriate?
 - CTEM, STEM.....
 - Image Coupled, Diffraction Coupled
- Obtain a typical spectrum
- Optimize the experimental conditions
 - Accelerating Voltage (maximum consistent with your specimen)
 - Choose the best Edges to analyze (K, L, M,.....)
 - Optimize β for the weakest edges ($\theta_E = \delta E / 2E_0$)
 - Optimize α to minimize problems ($\alpha < \beta/2$)
 - Optimize the Acquisition Mode
 - Normal - High Concentrations
 - Difference - Low Concentrations
 - Optimize the Data Acquisition
 - Select Energy Resolution and Range
 - DQE & Statistics
- Process the Data to Extract Intensities
 - Normal
 - Difference
 - Reference Spectra
- Check the relative specimen thickness ($t/\lambda < 1$)
- Calculate the compositions
 - Absolute # of atoms
 - Relative # of atoms
 - Standards/Standardless?
- ReCheck for Artifacts/Problems
 - Diffraction
 - Orientation/Channeling
 - Unidentified Edges
 - Spectral Overlaps
 - Radiation Damage

80

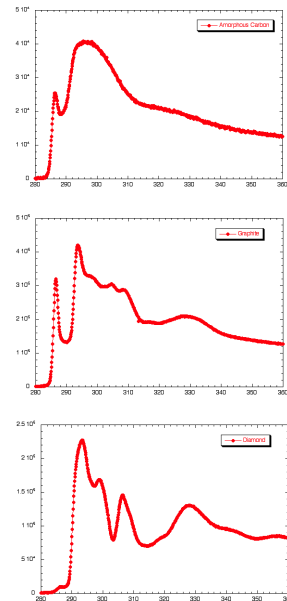
Linear Dichroism and Core Loss Electron Spectroscopy

Linear dichroism:

The linear polarization of the incident electrons parallel to the direction of momentum transfer. This polarization can be used to sense the anisotropy of the valence states involved in the core excitation process. It can detect the number or changes in the number of the valence holes in different directions of the atomic volume.



In many cases, the anisotropy of the charge in the atomic volume is caused by crystal-field interaction and is due to an anisotropy in the bonding.

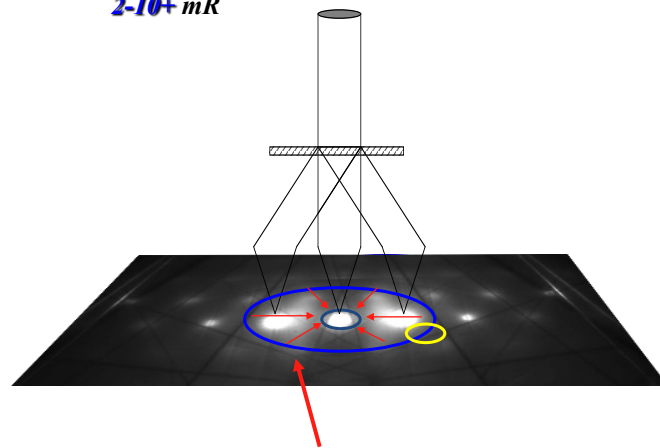


81

81

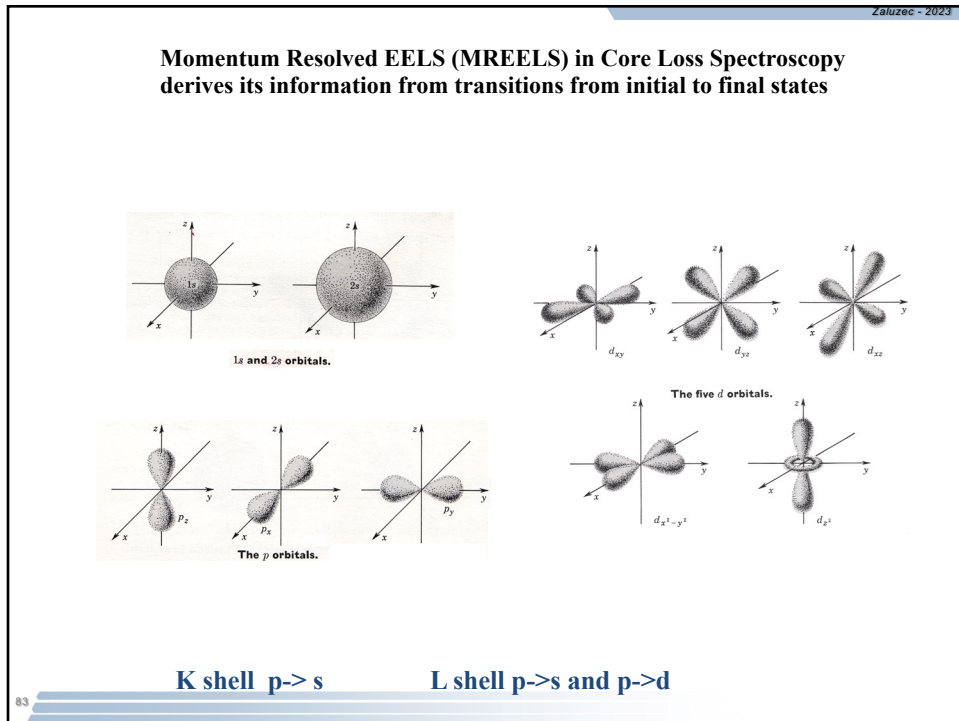
A Conventional EELS experiment in the TEM

Beam Convergence 2-10+ mR

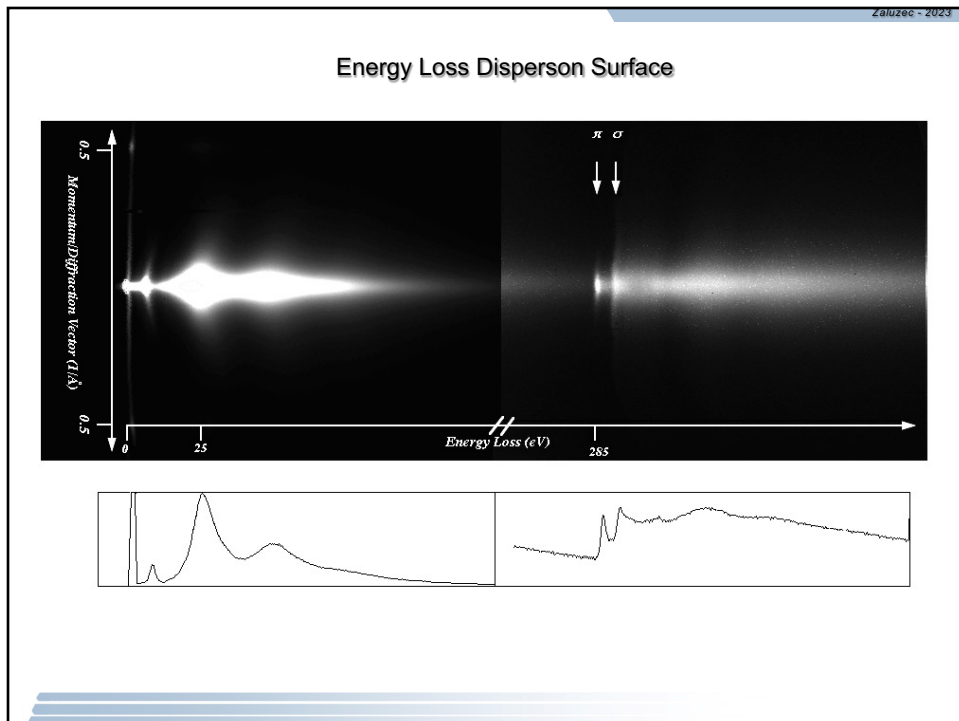


Angular Resolution typically 2-10 mR

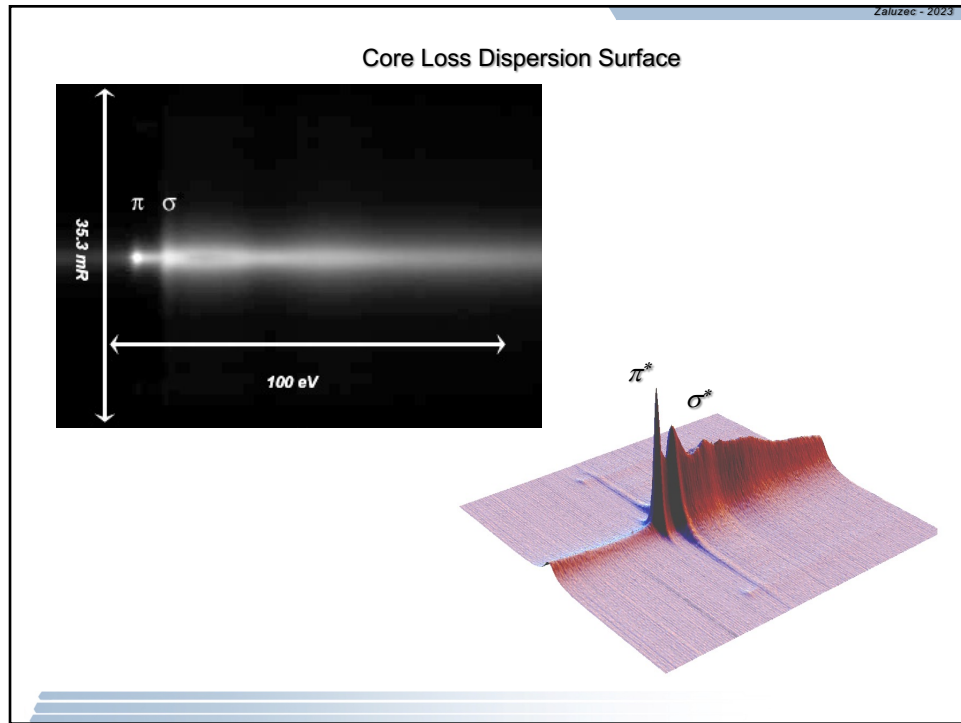
82



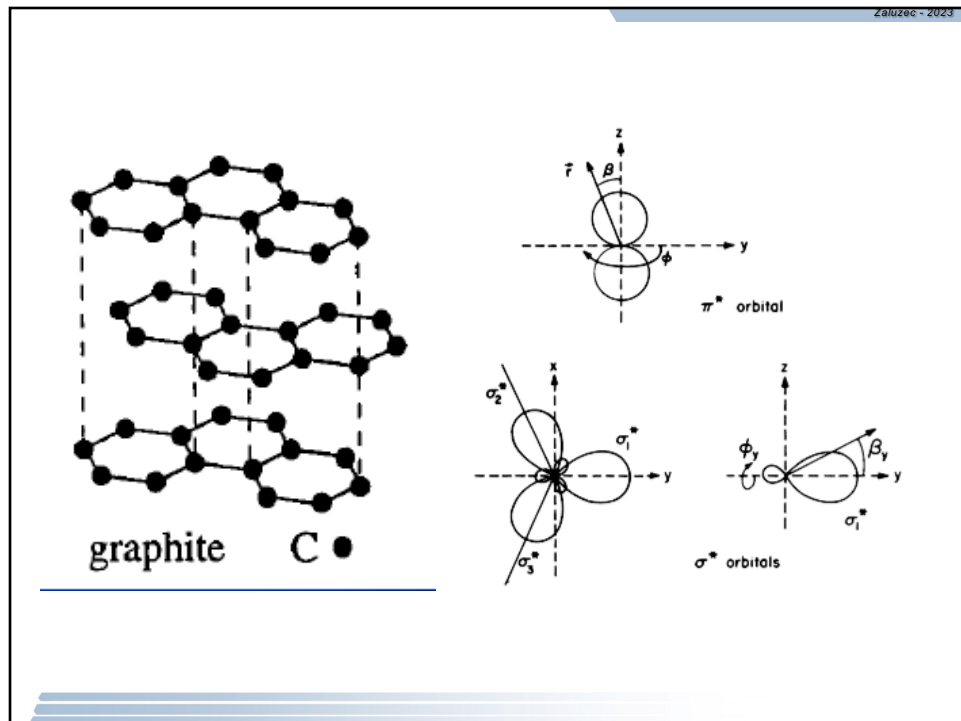
83



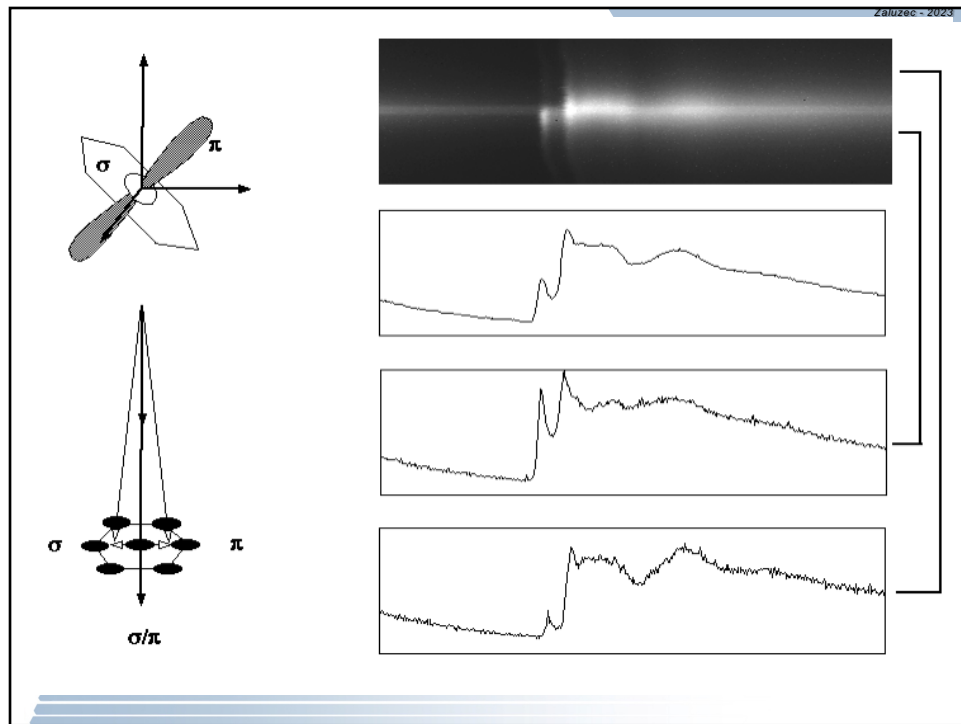
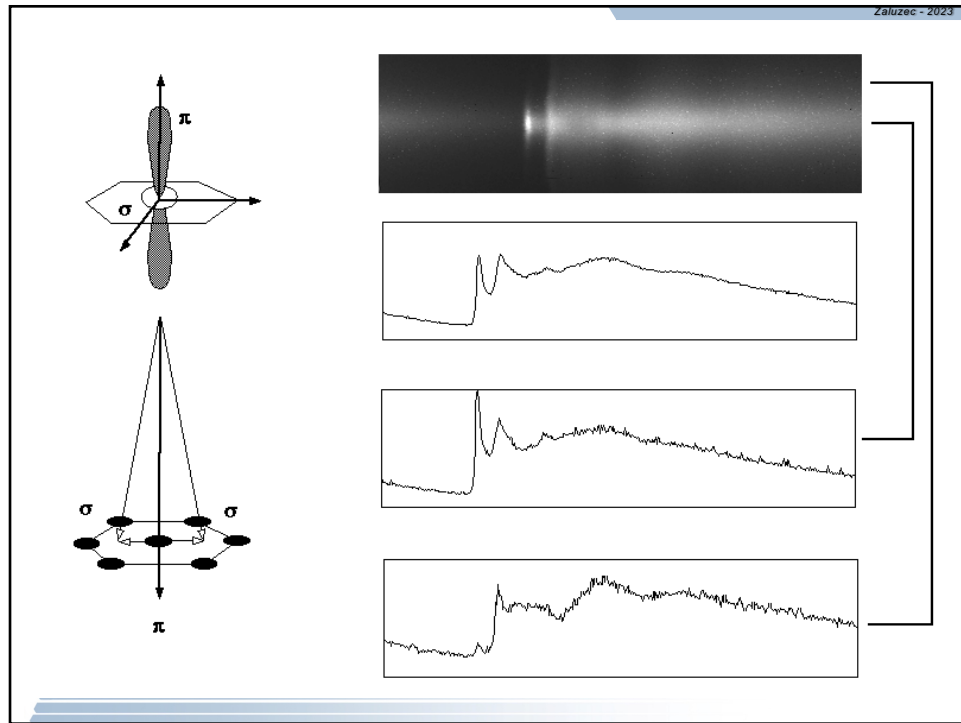
84

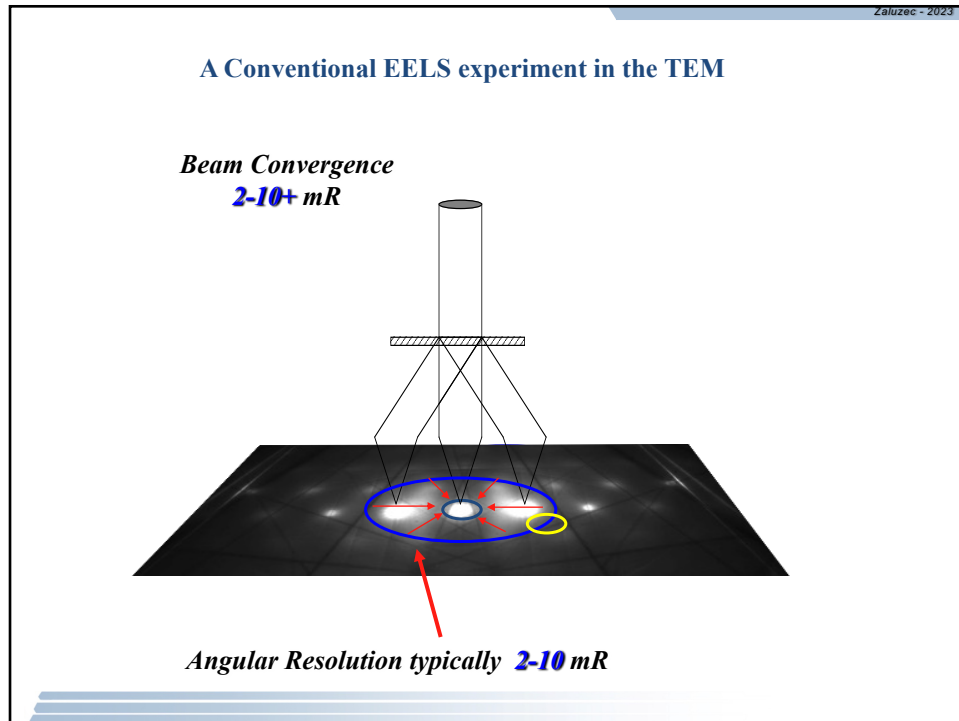


85

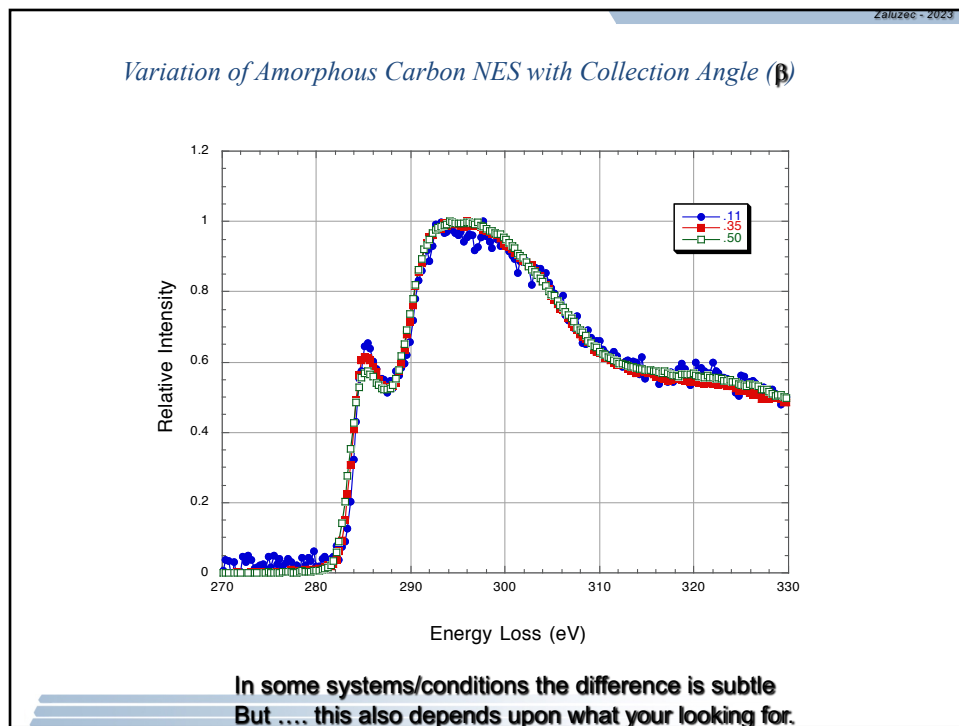


86



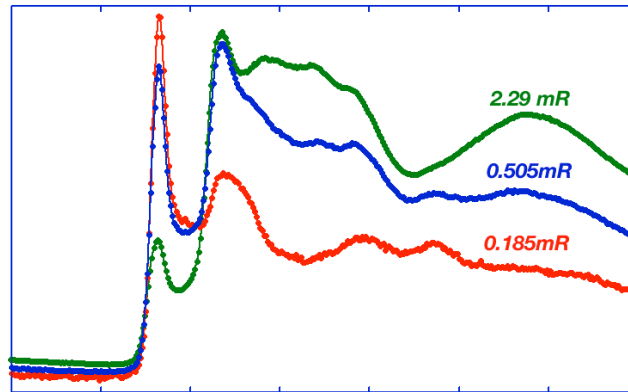


89



90

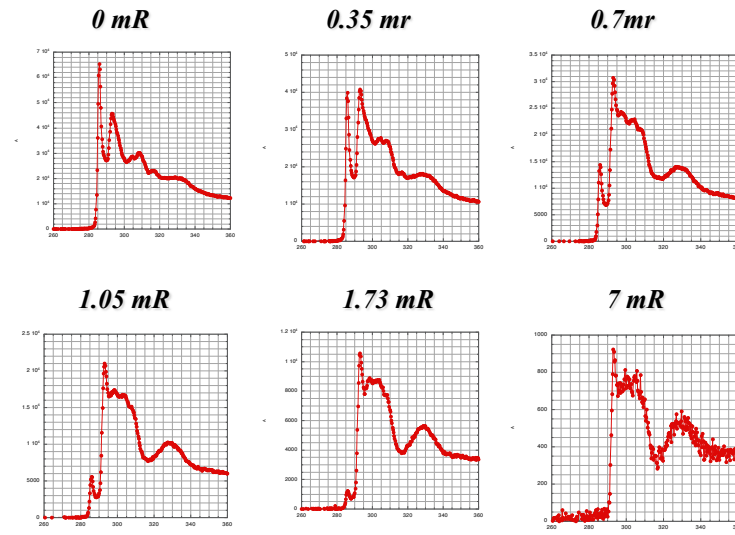
Variation of Graphite NES with Collection Angle (β)



For Anisotropic Materials there can be large variations in the relative intensities of spectral features as a function of Angle (Momentum)

91

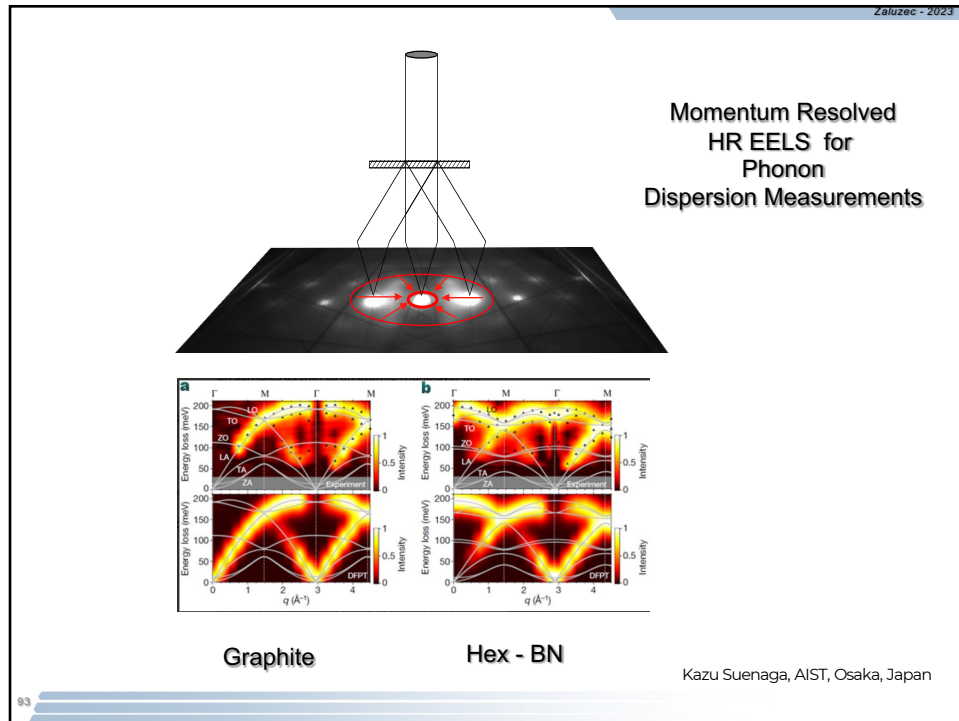
Variation of $C_K (\pi^* \sigma^*)$ in Graphite with Scattering Angle



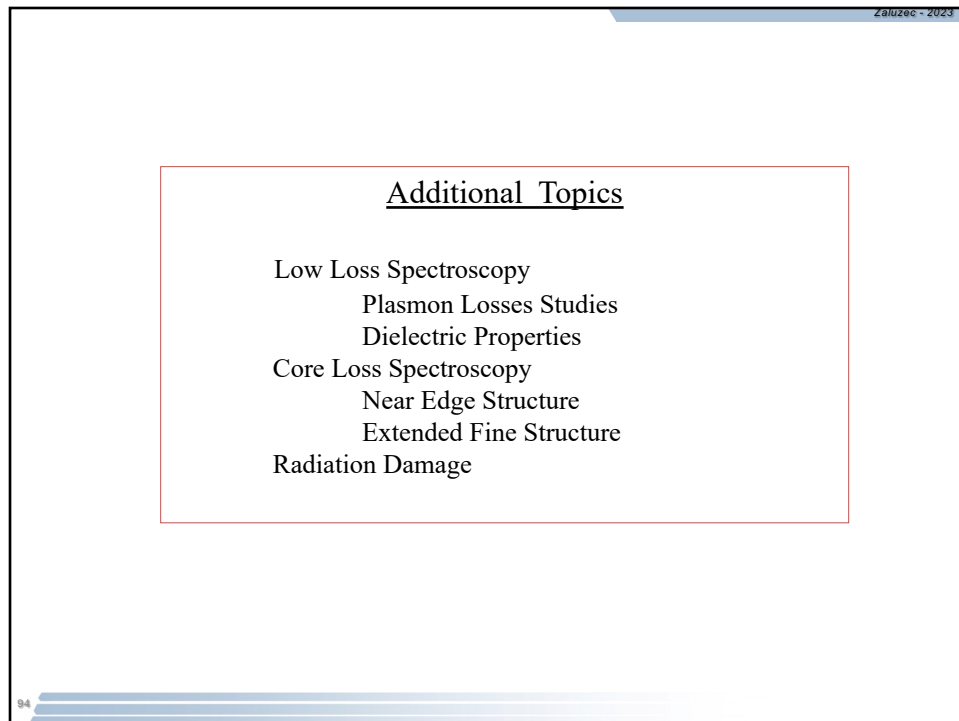
$\alpha_{1/2} \sim 0.025 \text{ mR}$ $\beta_{1/2} \sim 0.1 \text{ mR}$

$\theta_E \sim 1.15 \text{ mR}$

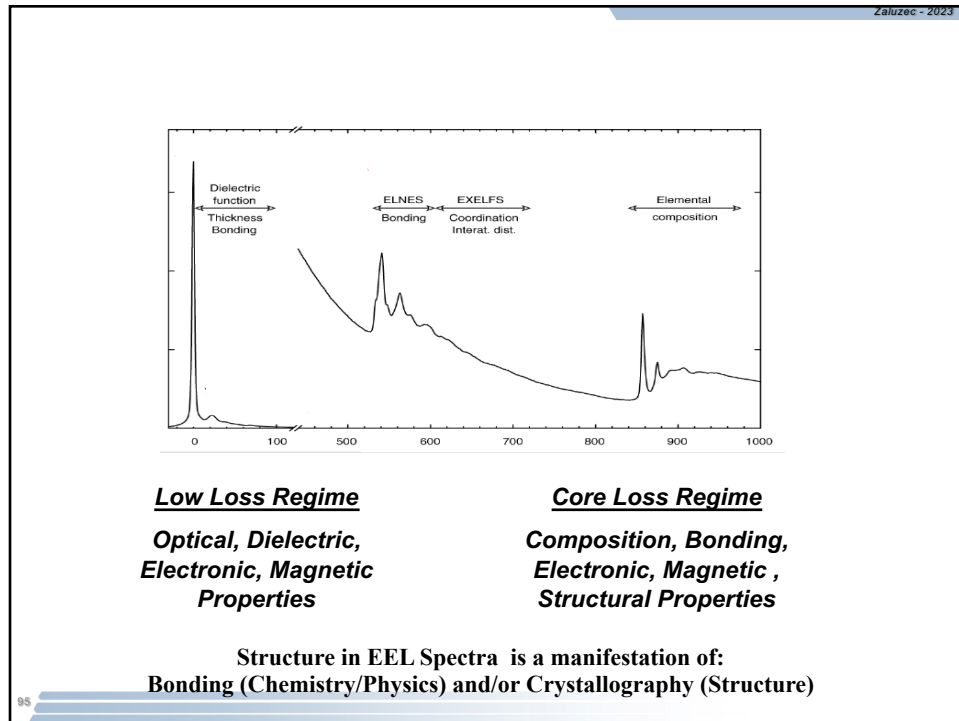
92



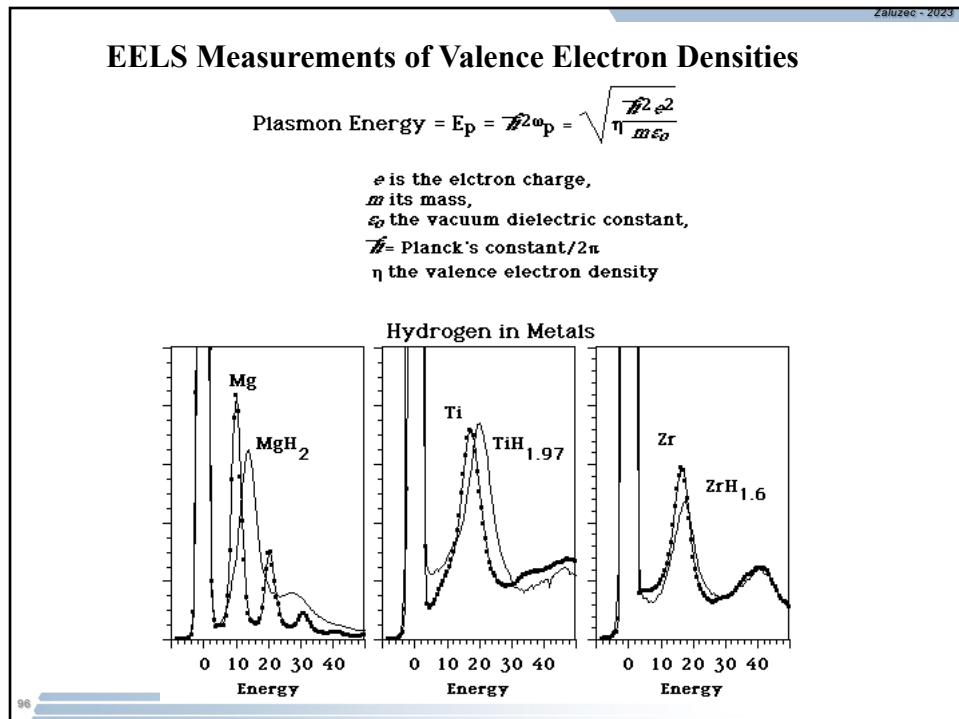
93



94



95



96

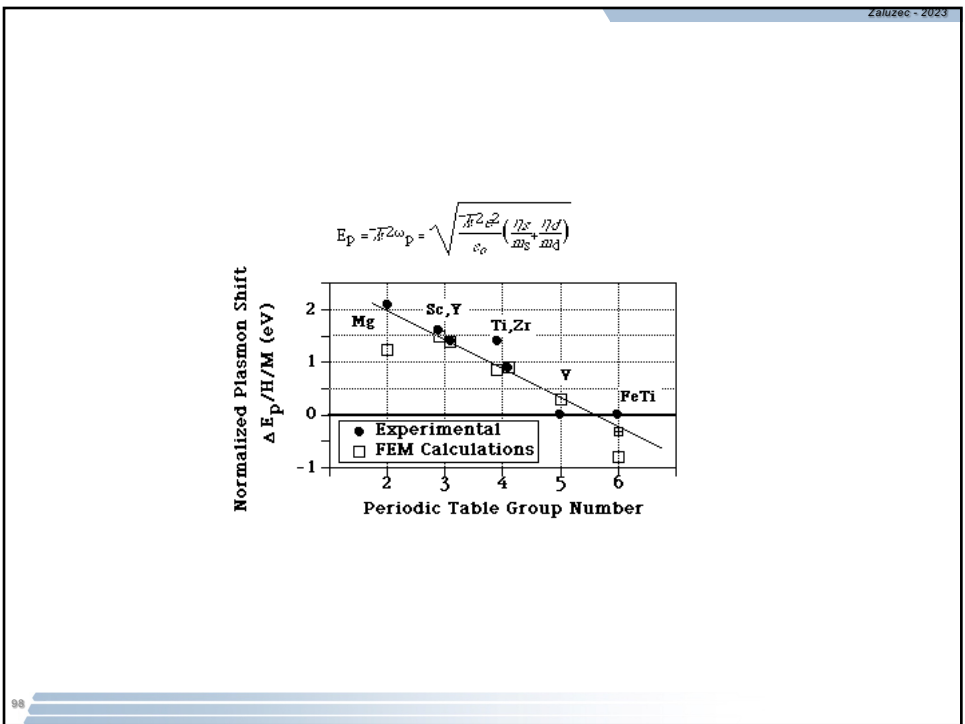
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**Table 2 Experimental and Calculated Plasmon Shifts
in Selected Metal-Hydrogen Systems**

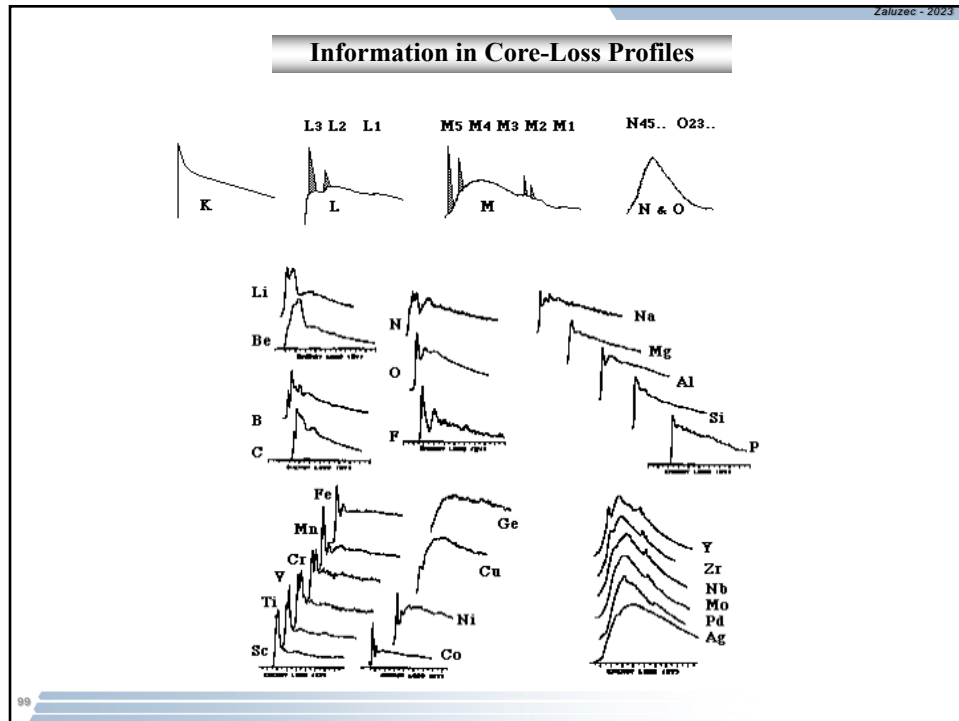
Material	Expt. E_p (eV)	Calculated FEM	$\Delta E_p/H/M$ Expt.	$\Delta E_p/H/M$ FEM Calc.
Group II				
Mg	10.0 ± 0.5	10.90	2.1 ± 0.7	1.24
MgH ₂	14.2 ± 0.5	13.38		
Group III				
Sc	14 ± 2 eV	12.87	1.6 ± 0.7	1.50
ScH ₂	17.2 ± 0.5	15.87		
Y	12.5 ± 0.2	11.19	1.4 ± 0.7	1.41
YH ₂	15.3 ± 0.5	14.0		
Group IV				
Ti	17.2 ± 0.5	17.69	1.4 ± 0.7	0.87
TiH _{1.97}	20.0 ± 0.5	19.4		
Zr	16.6 ± 0.5	15.37	0.9 ± 0.7	0.91
ZrH _{1.6}	18.1 ± 0.5	16.83		
Group V				
V	22.0 ± 0.5	22.29	0.0	0.3
VH _{0.5}	22.0 ± 0.5	22.44		
PseudoGroup VI				
FeTi	22.0 ± 0.5	25.04/21.9*		
FeTiH(β)	22.0 ± 0.5	24.65/21.8*	0.0	-0.84/-0.3*
FeTiH ₂ (γ)	22.0 ± 0.5	24.15/21.5*		

* Calculated using modified FEM with $m_s = m_e$ and $m_d = 1.9 m_e$

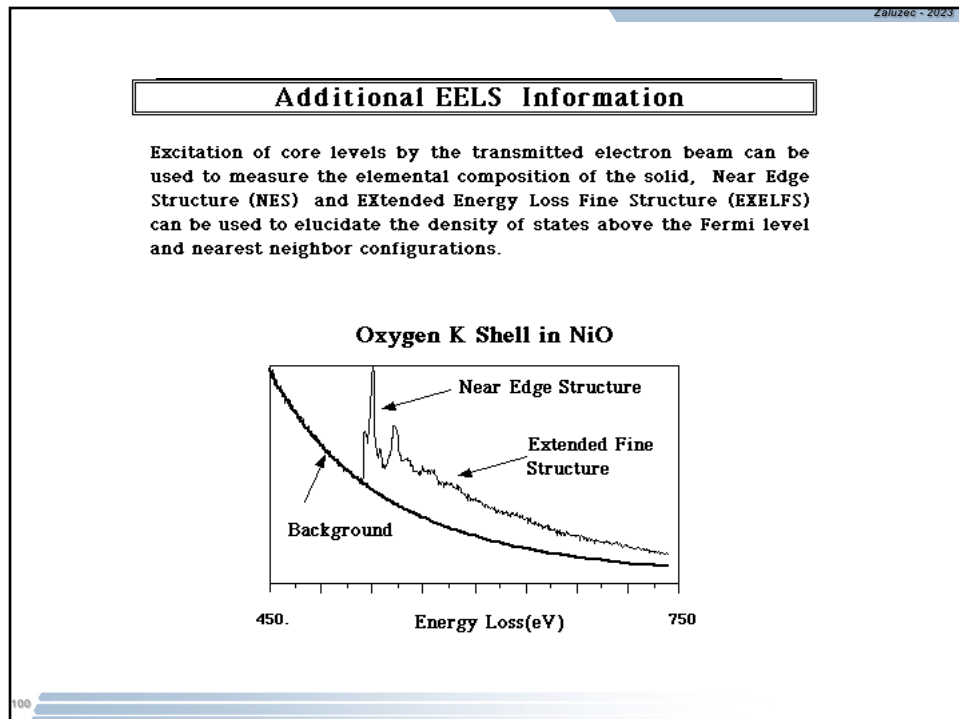
97



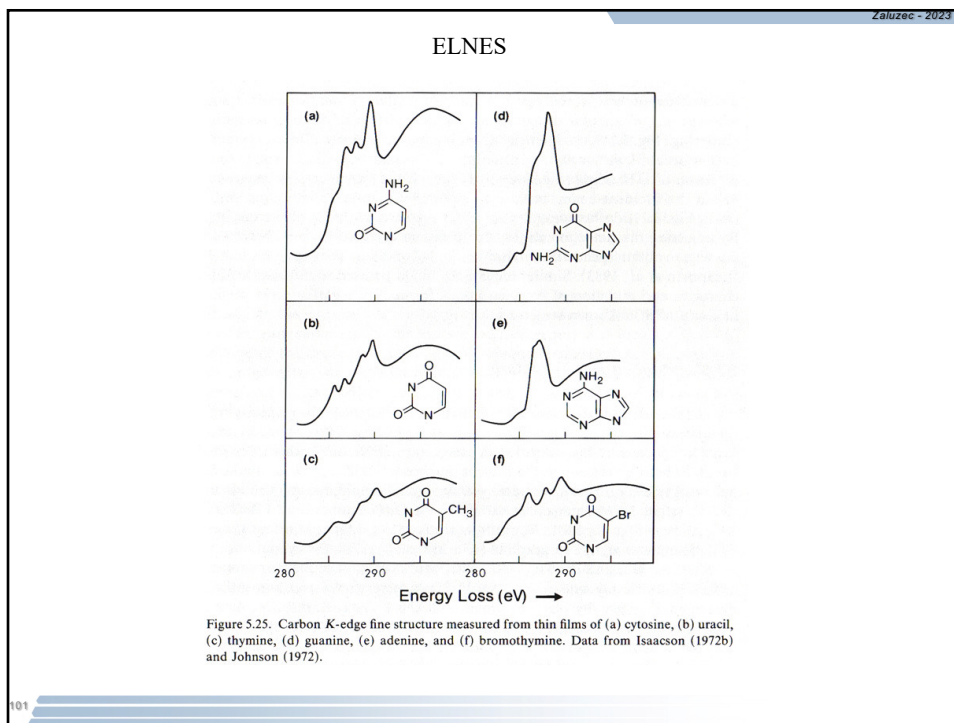
98



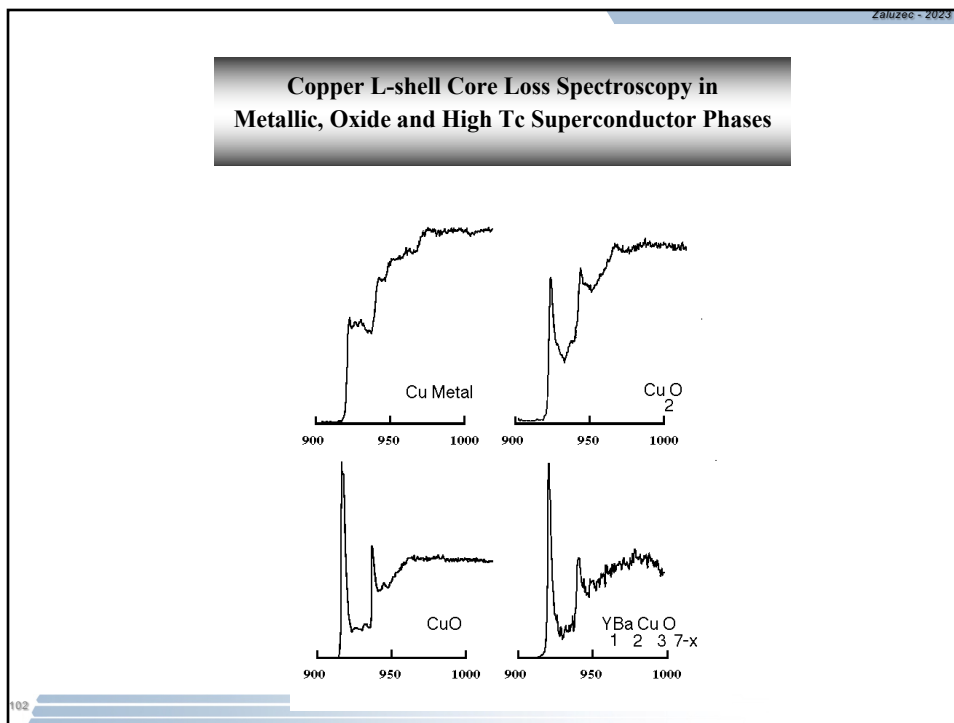
99



100



101

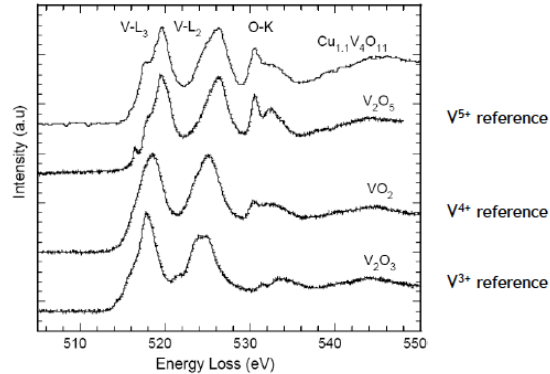


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Fingerprinting of different oxidation states by comparing the fine-structure of the experimental core-loss peak with that of reference structures

High resolution EELS of Cu-V oxides:
Application to batteries materials

Comparison between the V-L_{2,3} spectra of the Cu_{1.1}V₄O₁₁ and the reference vanadium oxides.
Comparison with reference spectra indicates that the vanadium is pentavalent.



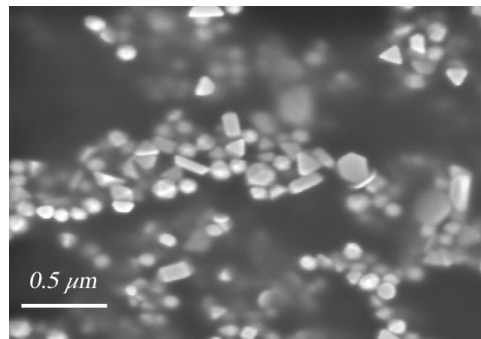
Laffont et al. Micron 37 (2006) 459, monochromized Tecnai 200ST (Delft)

103

103

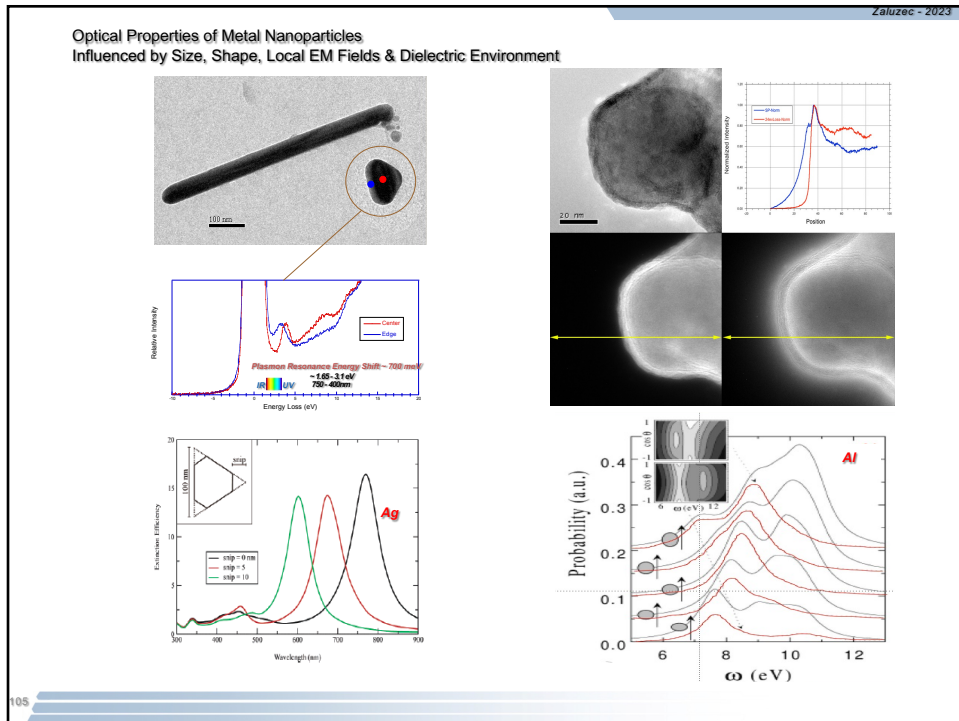
Optical Properties of Metallic Nanoparticles

- Optical properties of nanophase materials can be probed by EM radiation via excitation of **surface plasmon resonances (SPR'S)**.
- Surface Plasmon Resonances are collective excitations of valence/conduction electron
- Frequency/Width of the surface modes are dependent upon dielectric constants of the nanostructures size, shape and local environment
- Requires excellent energy resolution in EEL Spectroscopy Mode to accurately measure.

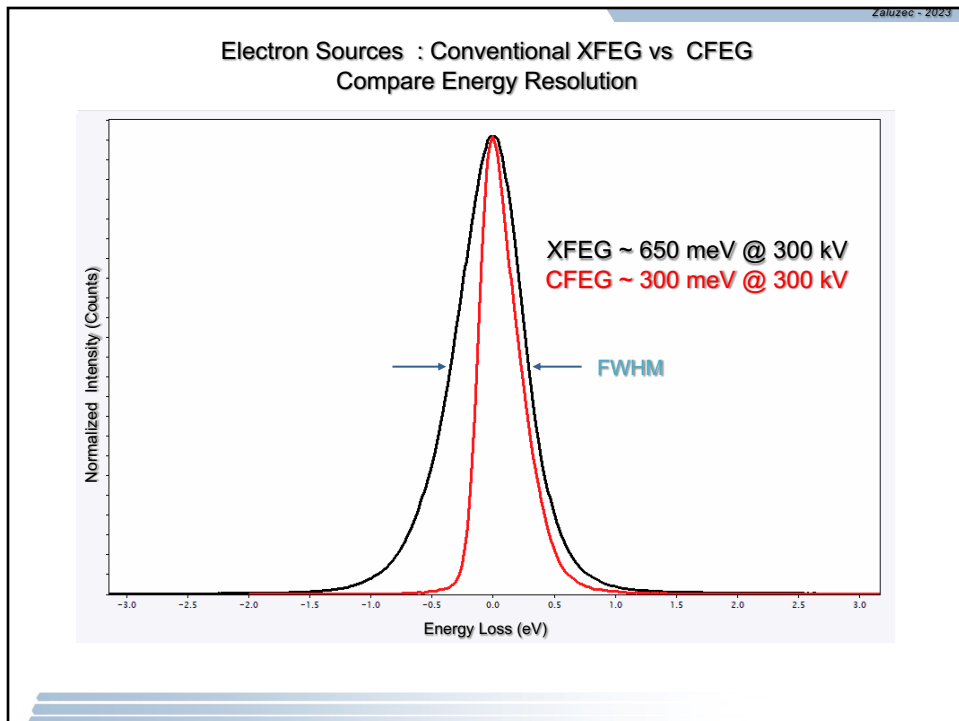


104

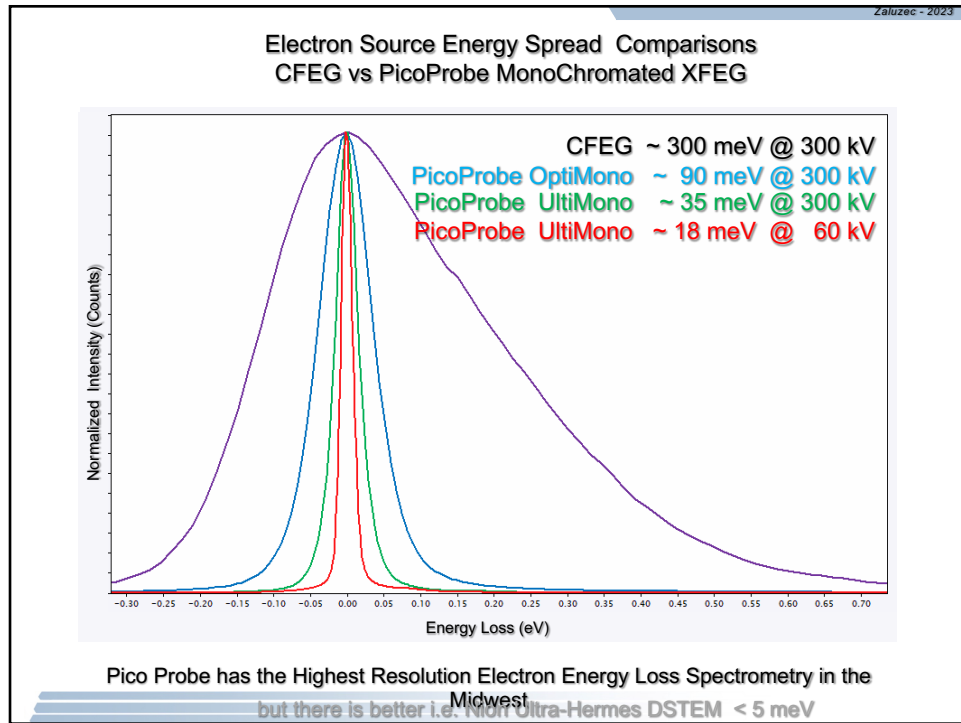
104



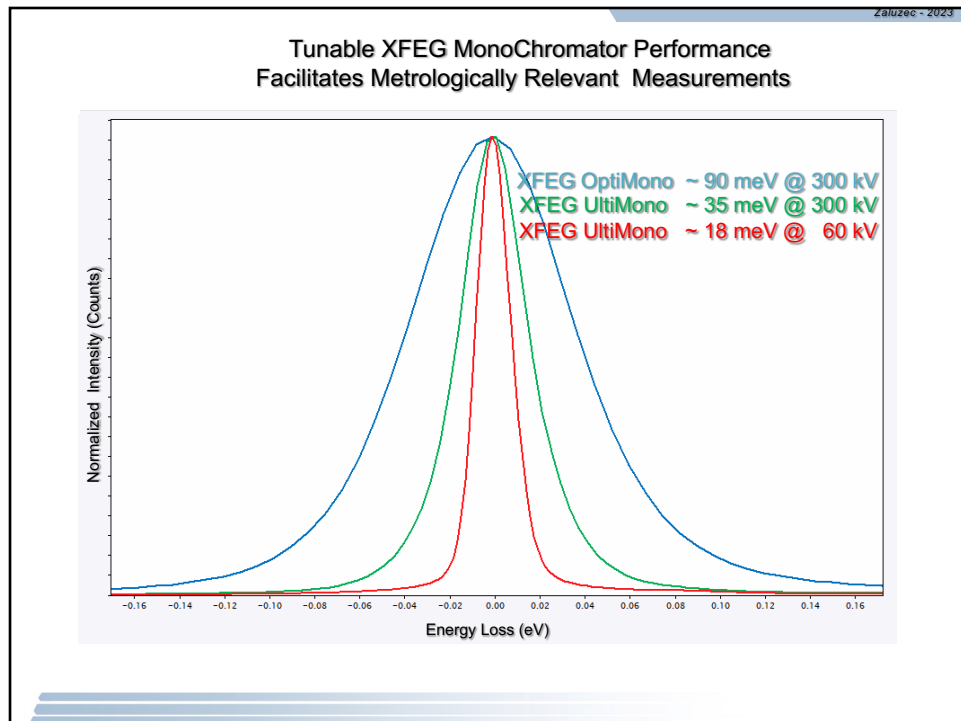
105



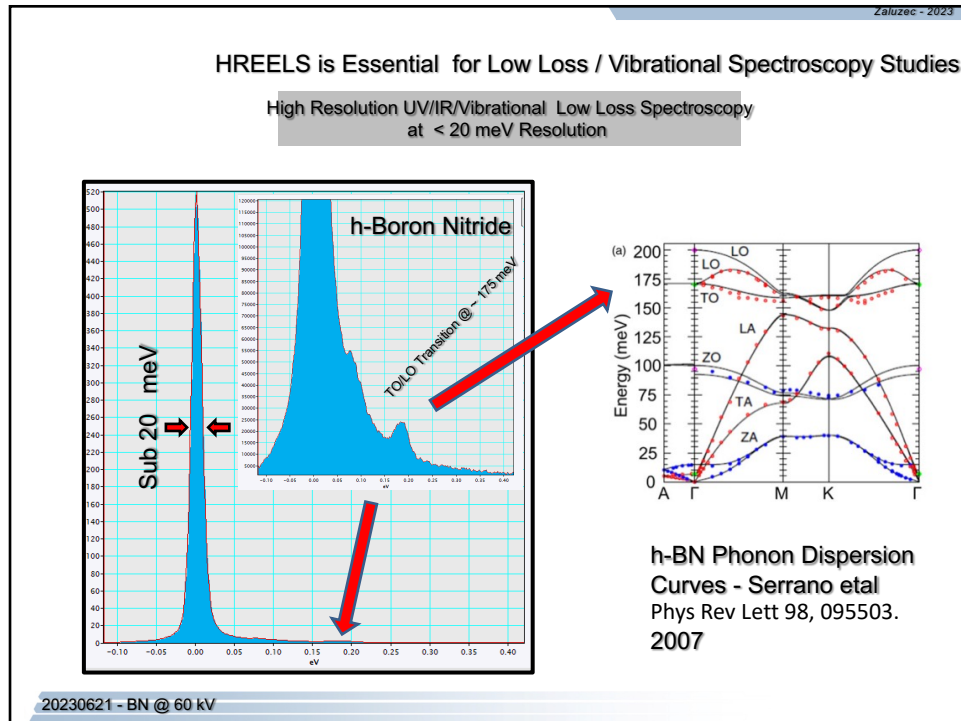
106



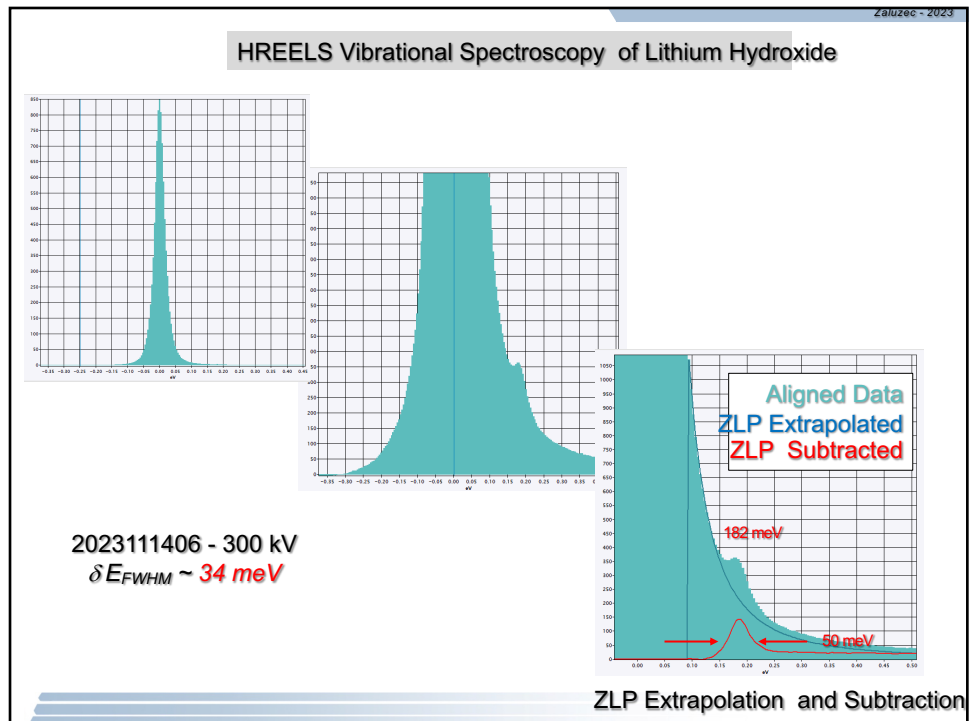
107



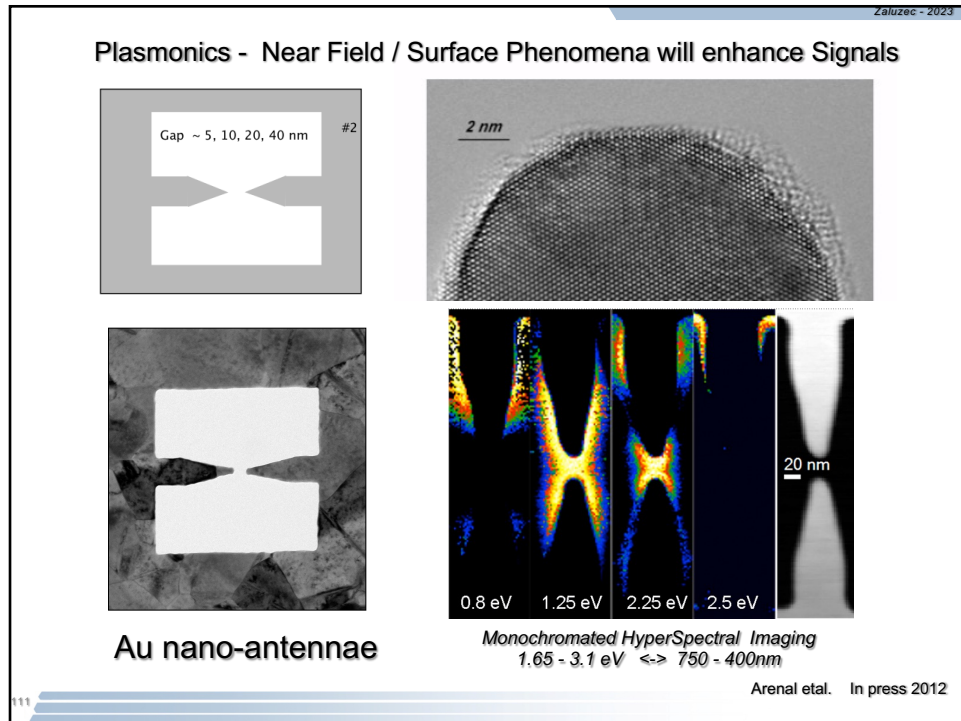
108



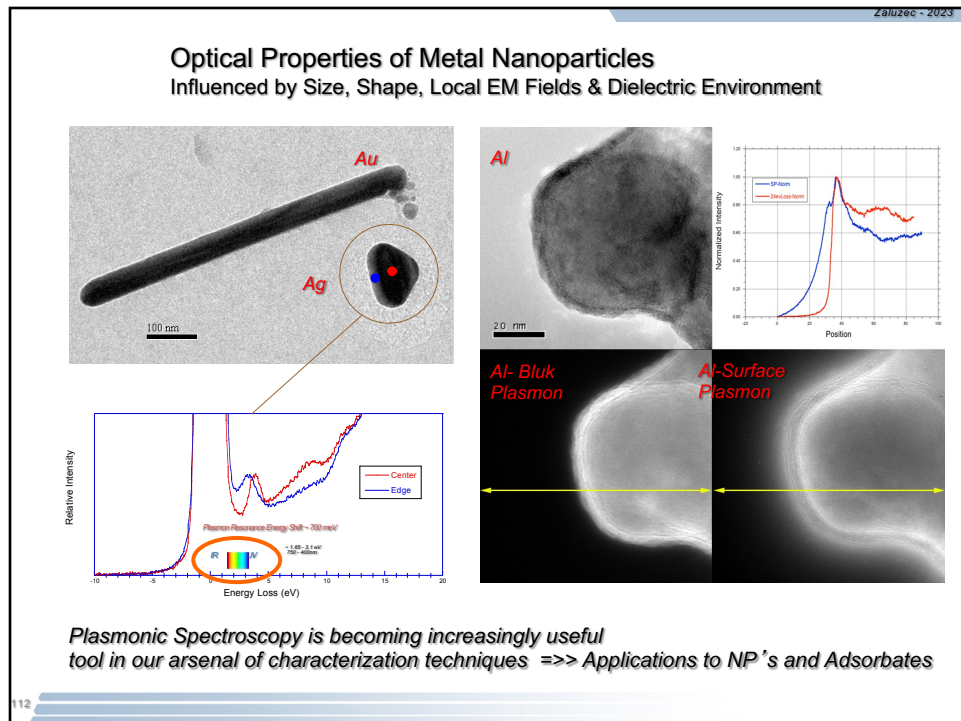
109



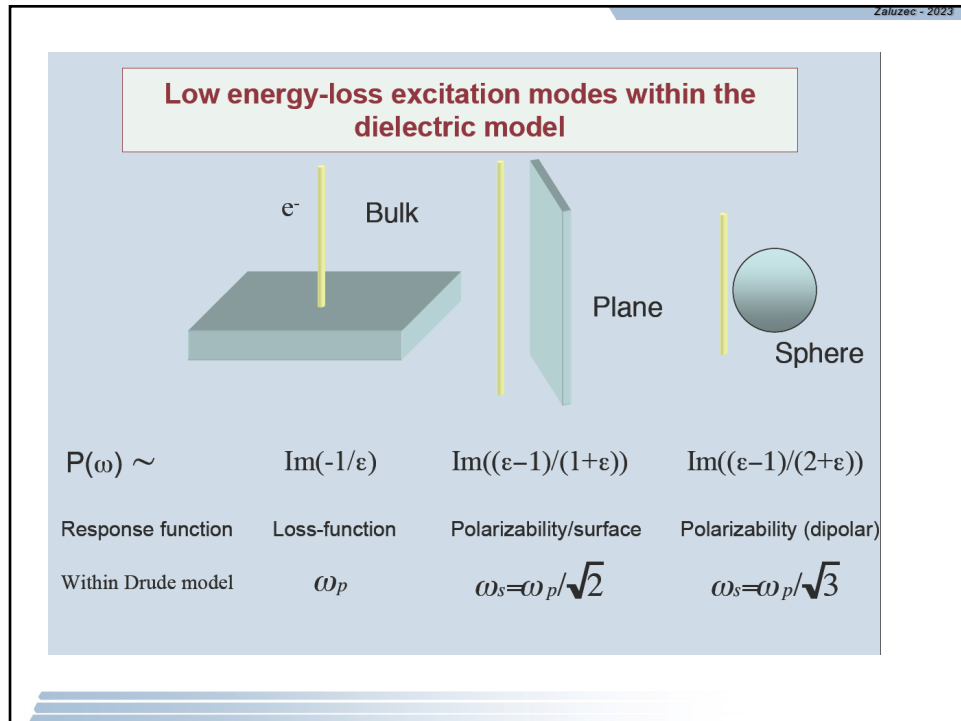
110



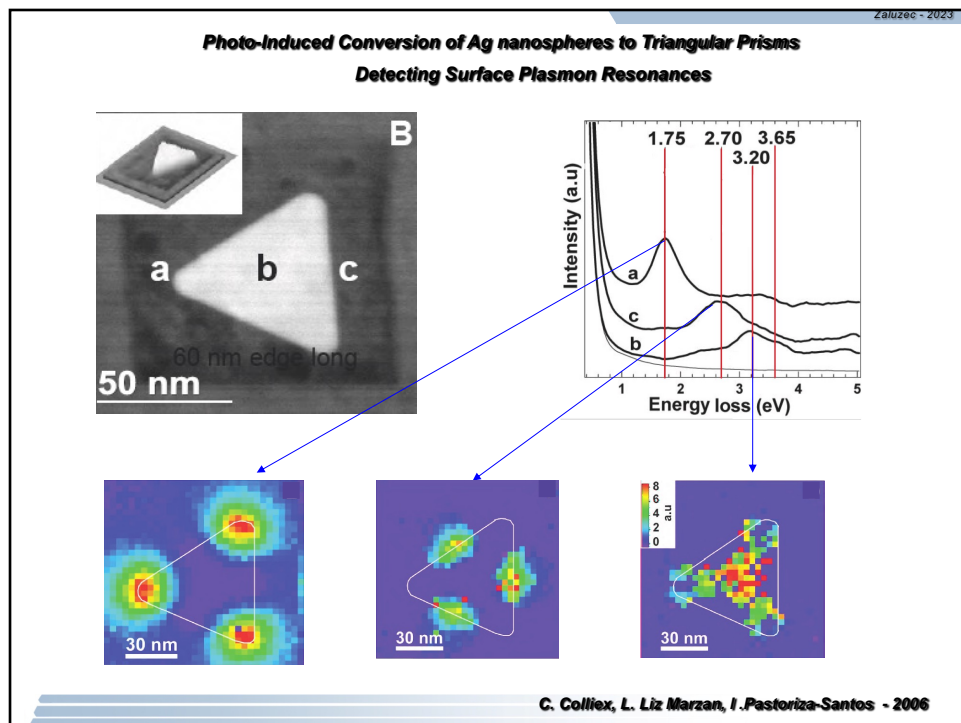
111



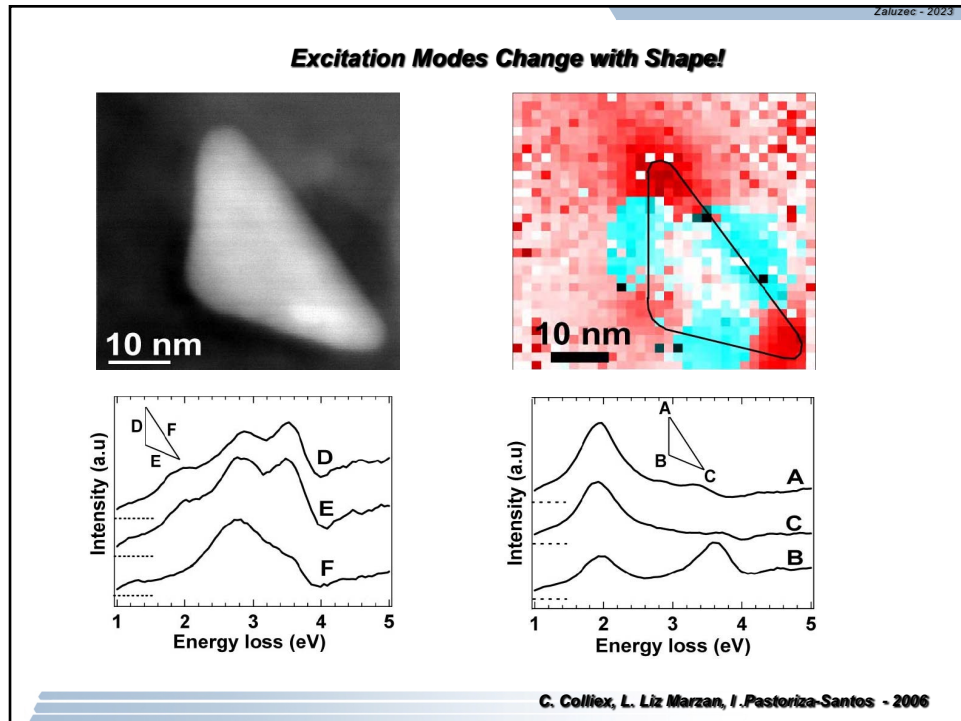
112



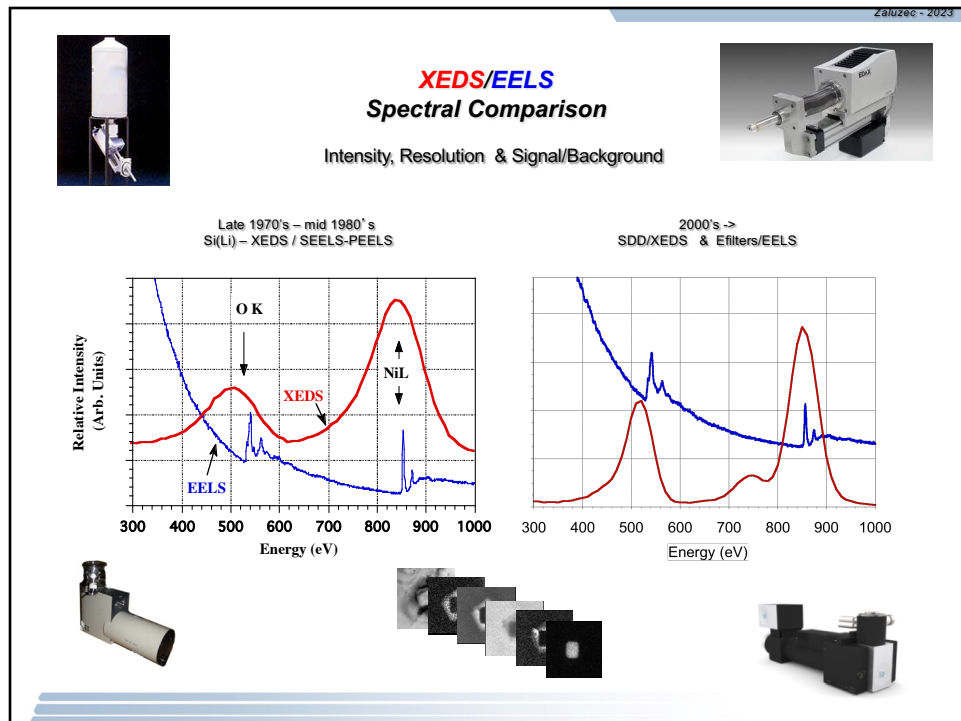
113



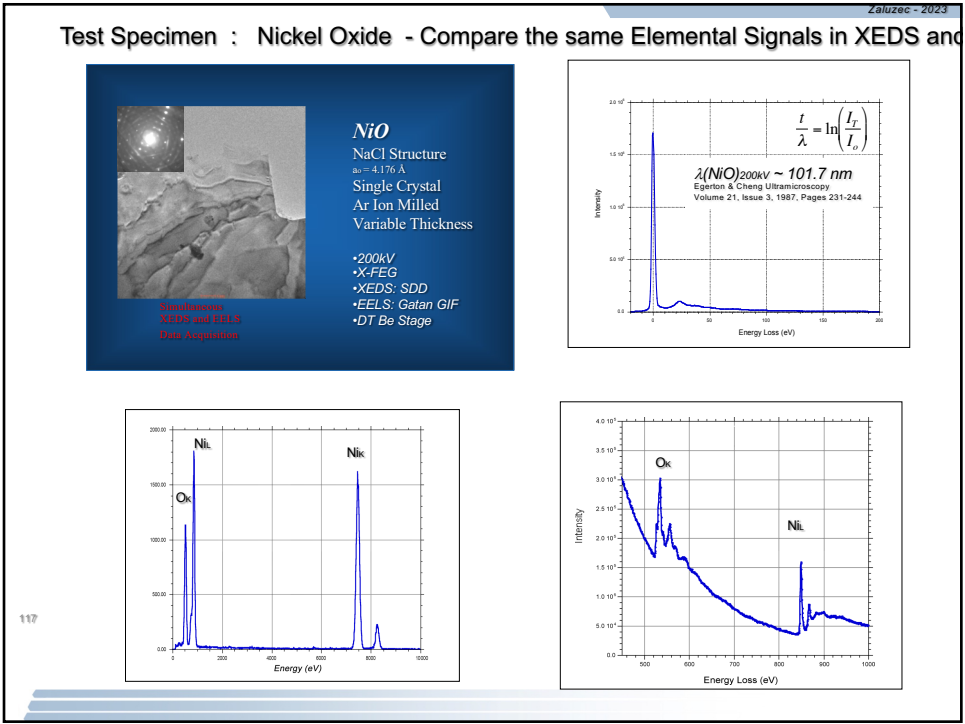
114



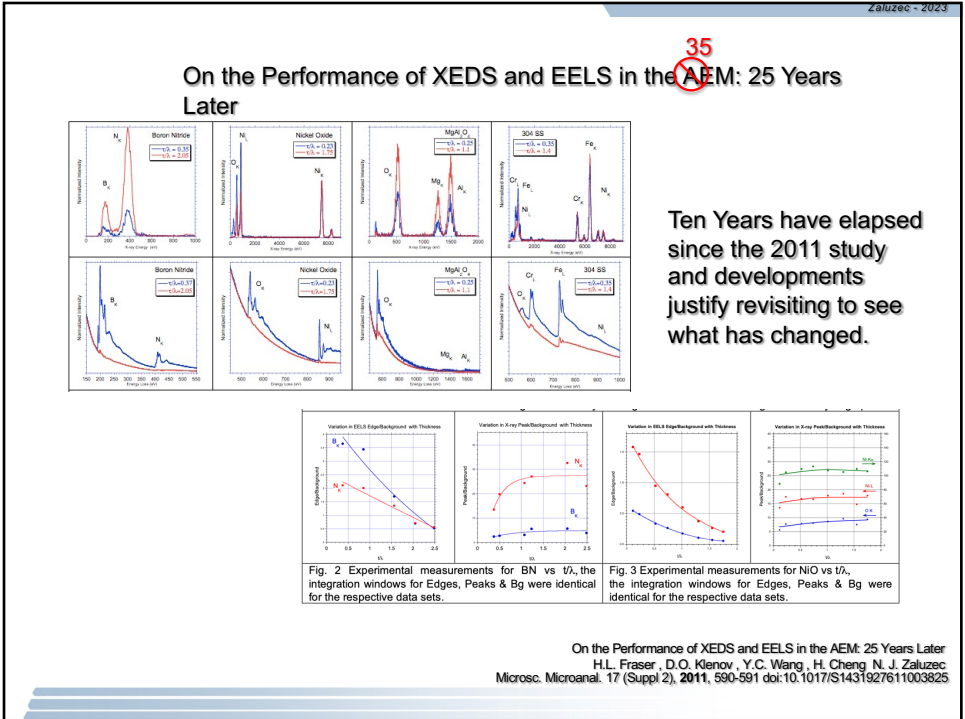
115



116

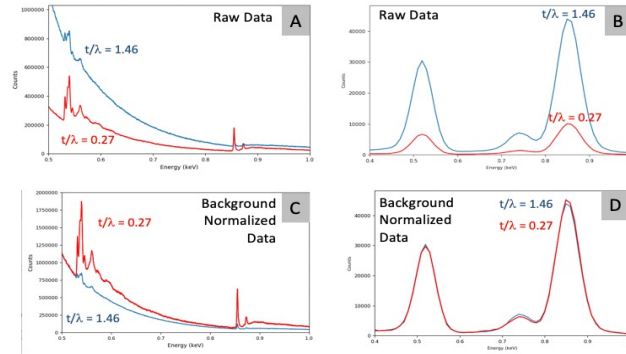


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Measurements - JEOL Mono NEOARM 200 F @ Chalmers University

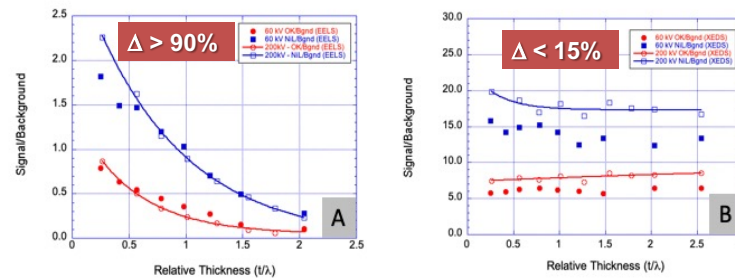


Comparison of EELS and XEDS showing the O_K and NiL signals for two values of t/λ .
A & B are raw data, while C & D are normalized at the O_K background values.

Dual JEOL 100 mm² XEDS & Gatan Quantum HR.

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Measurements – NiO JEOL Mono NEOARM 200 F @ Chalmers University @ 60 kV & 200 kV



Experimental variation in the Signal/Background for EELS (A) and XEDS (B) measurements as a function of relative thickness at 60 and 200 kV. Solid lines are guides to the eye for 200 keV data. Note the relatively uniform I/B for XEDS vs EELS.

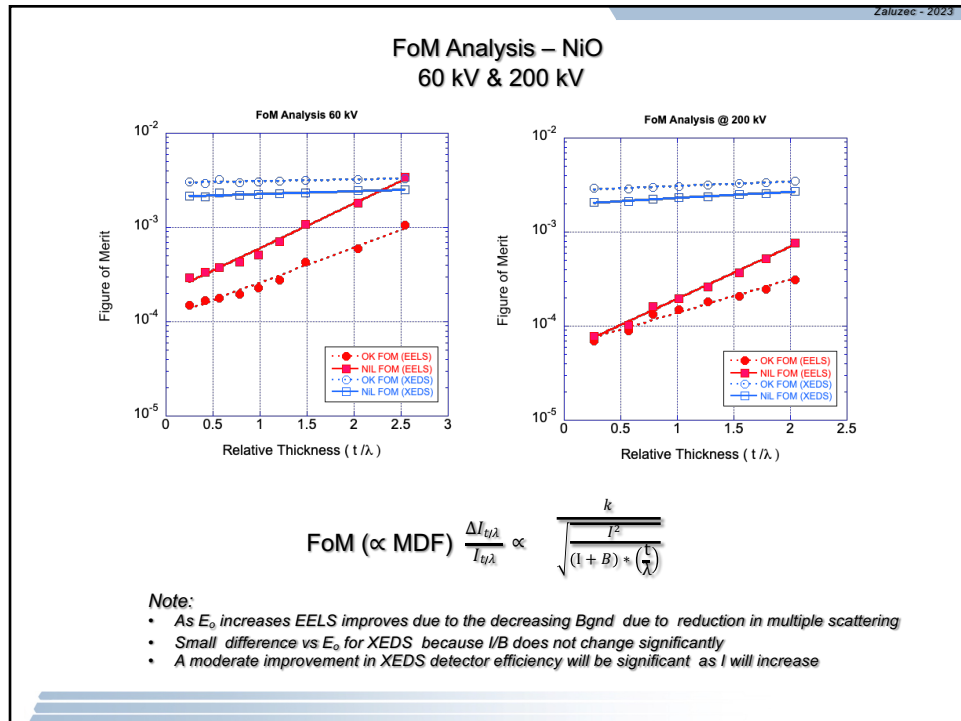
$$\frac{\Delta I}{I} \propto \text{MDF} \propto \frac{k}{\sqrt{\frac{I^2}{(1+B)}}}$$

Both I & B vary with thickness

$$\text{FoM} (\propto \text{MDF}) \frac{\Delta I_{t/\lambda}}{I_{t/\lambda}} \propto \frac{k}{\sqrt{\frac{I^2}{(1+B) * (\frac{t}{\lambda})}}}$$

Thickness Normalization

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There are always Limiting Factors

	Geometrical Broadening (all probes) $d_G \sim 2\alpha t$	α semiangle t thickness
	Beam Broadening (general scattering) $d_B \sim 625 \frac{Z}{E_0} \left(\sqrt{\frac{\rho}{A}} \right) t^{3/2}$	d_B (cm) t thickness (cm) ρ density (gm/cm³) E_0 Accelerating Voltage (keV) Z, A atomic number & wt
	Chromatic Broadening (EFTEM) $d_C \sim FC\beta \frac{\Delta_s}{E_0}$	C_c Chromatic Ab Coeff (mm $\rightarrow$ μm) β Scattering semiangle (mR) Δ_s Energy Window/Slit Width (eV) E_0 Accelerating Voltage (keV) F Factor 0.1 (low loss) -0.3 (high loss)
	Inelastic Delocalization $d_L \sim 0.44 \frac{\lambda}{\theta_E^{3/4}}$	$\theta_E = \frac{\Delta E}{2T_0}$ $T_0 = \gamma m_0 c^2$ λ Electron Wavelength θ_E Mean Scattering angle ΔE Energy Loss T_0 Electron Kinetic Energy
	Image/Diffraction Delocalization $d_R = C_5 \square^5 g^5 + C_3 \square^3 g^3 + \square \square f g _{\max}$	$C_3 = C_s$ g diffract. vector Δf defocus

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Table 2.1. Summary of the analytical uses of EELS

Property determined	Spectral region	Processing required	Uses/limitations
Sample thickness	Full spectrum or low loss region	Integration of intensities	Rapid measure of relative thickness; need Λ (inelastic) for absolute values.
Valence electron density	Low loss – plasmon peak position	Peak fitting if required	Phase Identification/ Effects of alloying
Surface/interface states	Low loss – surface plasmons	Need model of dielectric function based on geometry	Surface properties
Joint DOS	Low loss – energy loss function	Deconvolution/fitting of ZLP/Kramers Kronig analysis/sum rules	Band gaps/interband transitions/comparison with optical results
Elemental concentration/ elemental distributions (EFTEM)	High loss – ionization edge intensities	Background subtraction/ deconvolution/ integration/calculation of partial cross-sections	Good for light elements with edges in range 0–2.5 keV/ often high detection limits/limited to thin sample areas
Element specific local coordination and/or valency	High loss – ELNES	Deconvolution/ comparison with reference materials – fingerprinting/peak fitting	Need good energy resolution and determination of absolute energy loss
Element specific unoccupied DOS	High loss – ELNES	Deconvolution/modelling of electronic structure	Need good energy resolution/effect of the core hole
Element specific radial distribution function	High loss – EXELFS	Standard EXAFS data processing	Low SNR – requires good statistics and large edge separations
Anisotropic DOS	High loss – ELNES/ low loss	Deconvolution/modelling of electronic structure	Need small collection angles and well-defined specimen orientation
Site specific DOS	High loss – ELNES/ALCHEMI	Deconvolution/modelling of electronic structure	Need well-defined diffraction and collection conditions
Ground state electron momentum distribution at large momentum transfer	Compton profile	Standard Compton scattering data processing	Low SNR/diffraction conditions